Computer Architecture

Lecture 13: Emerging Memory Technologies

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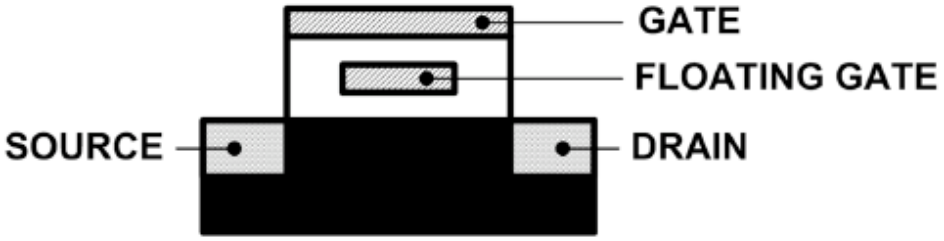
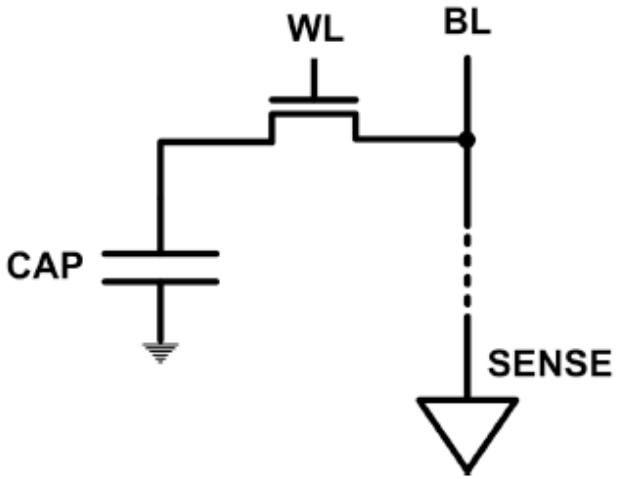
Emerging Memory Technologies

Limits of Charge Memory

- Difficult charge placement and control
  - Flash: floating gate charge
  - DRAM: capacitor charge, transistor leakage
- Reliable sensing becomes difficult as charge storage unit size reduces





Solution 1: New Memory Architectures

- Overcome memory shortcomings with
  - Memory-centric system design
  - Novel memory architectures, interfaces, functions
  - Better waste management (efficient utilization)

- Key issues to tackle
  - Enable reliability at low cost → high capacity
  - Reduce energy
  - Reduce latency
  - Improve bandwidth
  - Reduce waste (capacity, bandwidth, latency)
  - Enable computation close to data

Solution 1: New Memory Architectures

- Liu+, "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.
- Kim+, "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.
- Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.
- Liu+, "An Experimental Study of Data Retention Behavior in Modern DRAM Devices," ISCA 2013.
- Seshadri+, "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.
- Pekhimenko+, "Linearly Compressed Pages: A Main Memory Compression Framework," MICRO 2013.
- Chang+, "Improving DRAM Performance by Parallelizing Refreshes with Accesses," HPCA 2014.
- Khan+, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," SIGMETRICS 2014.
- Luo+, "Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost," DSN 2014.
- Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.
- Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.
- Qureshi+, "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems," DSN 2015.
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field," DSN 2015.
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- Seshadri+, "Fast Bulk Bitwise AND and OR in DRAM," IEEE CAL 2015.
- Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing," ISCA 2015.
- Ahn+, "PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture," ISCA 2015.
- Lee+, "Decoupled Direct Memory Access: Isolating CPU and IO Traffic by Leveraging a Dual-Data-Port DRAM," PACT 2015.
- Seshadri+, "Gather-Scatter DRAM: In-DRAM Address Translation to Improve the Spatial Locality of Non-unit Strided Accesses," MICRO 2015.
- Lee+, "Simultaneous Multi-Layer Access: Improving 3D-Stacked Memory Bandwidth at Low Cost," TACO 2016.
- Hassan+, "ChargeCache: Reducing DRAM Latency by Exploiting Row Access Locality," HPCA 2016.
- Chang+, "Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Migration in DRAM," HPCA 2016.
- Chang+, "Understanding Latency Variation in Modern DRAM Chips Experimental Characterization, Analysis, and Optimization," SIGMETRICS 2016.
- Khan+, "PARBOR: An Efficient System-Level Technique to Detect Data Dependent Failures in DRAM," DSN 2016.
- Hsieh+, "Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems," ISCA 2016.
- Hashemi+, "Accelerating Dependent Cache Misses with an Enhanced Memory Controller," ISCA 2016.
- Boroumand+, "LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory," IEEE CAL 2016.
- Pattnaik+, "Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities," PACT 2016.
- Hsieh+, "Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation," ICCD 2016.
- Hashemi+, "Continuous Runahead: Transparent Hardware Acceleration for Memory Intensive Workloads," MICRO 2016.
- Khan+, "A Case for Memory Content-Based Detection and Mitigation of Data-Dependent Failures in DRAM"," IEEE CAL 2016.
- Hassan+, "SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies," HPCA 2017.
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- Lee+, "Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms," SIGMETRICS 2017.
- Chang+, "Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms," SIGMETRICS 2017.
- Patel+, "The Reach Profiler (REAPER): Enabling the Mitigation of DRAM Retention Failures via Profiling at Aggressive Conditions," ISCA 2017.
- Seshadri and Mutlu, "Simple Operations in Memory to Reduce Data Movement," ADCOM 2017.
- Liu+, "Concurrent Data Structures for Near-Memory Computing," SPAA 2017.
- Khan+, "Detecting and Mitigating Data-Dependent DRAM Failures by Exploiting Current Memory Content," MICRO 2017.
- Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology," MICRO 2017.
- Kim+, "GRIM-Filter: Fast Seed Location Filtering in DNA Read Mapping Using Processing-in-Memory Technologies," BMC Genomics 2018.
- Kim+, "The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern DRAM Devices," HPCA 2018.
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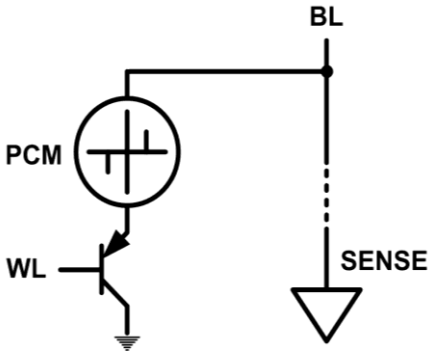
- Das+, "VRL-DRAM: Improving DRAM Performance via Variable Refresh Latency," DAC 2018.
- Ghose+, "What Your DRAM Power Models Are Not Telling You: Lessons from a Detailed Experimental Study," SIGMETRICS 2018.
- Kim+, "Solar-DRAM: Reducing DRAM Access Latency by Exploiting the Variation in Local Bitlines," ICCD 2018.
- Wang+, "Reducing DRAM Latency via Charge-Level-Aware Look-Ahead Partial Restoration," MICRO 2018.
- Avoid DRAM:
  - Seshadri+, "The Evicted-Address Filter: A Unified Mechanism to Address Both Cache Pollution and Thrashing," PACT 2012.
  - Pekhimenko+, "Base-Delta-Immediate Compression: Practical Data Compression for On-Chip Caches," PACT 2012.
  - Seshadri+, "The Dirty-Block Index," ISCA 2014.
  - Pekhimenko+, "Exploiting Compressed Block Size as an Indicator of Future Reuse," HPCA 2015.
  - Vijaykumar+, "A Case for Core-Assisted Bottleneck Acceleration in GPUs: Enabling Flexible Data Compression with Assist Warps," ISCA 2015.
  - Pekhimenko+, "Toggle-Aware Bandwidth Compression for GPUs," HPCA 2016.

Solution 2: Emerging Memory Technologies

- Some emerging **resistive** memory technologies seem more scalable than DRAM (and they are non-volatile)

- Example: Phase Change Memory
  - Data stored by changing phase of material
  - Data read by detecting material's resistance
  - Expected to scale to 9nm (2022 [ITRS 2009])
  - Prototyped at 20nm (Raoux+, IBM JRD 2008)
  - Expected to be denser than DRAM: can store multiple bits/cell



- But, emerging technologies have (many) shortcomings
  - Can they be enabled to replace/augment/surpass DRAM?

Solution 2: Emerging Memory Technologies

- Lee+, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA'09, CACM'10, IEEE Micro'10.
- Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters 2012.
- Yoon, Meza+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012.
- Kultursay+, "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.
- Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.
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- Zhao+, "FIRM: Fair and High-Performance Memory Control for Persistent Memory Systems," MICRO 2014.
- Yoon, Meza+, "Efficient Data Mapping and Buffering Techniques for Multi-Level Cell Phase-Change Memories," TACO 2014.
- Ren+, "ThyNVM: Enabling Software-Transparent Crash Consistency in Persistent Memory Systems," MICRO 2015.
- Chauhan+, "NVMove: Helping Programmers Move to Byte-Based Persistence," INFLOW 2016.
- Li+, "Utility-Based Hybrid Memory Management," CLUSTER 2017.
- Yu+, "Banshee: Bandwidth-Efficient DRAM Caching via Software/Hardware Cooperation," MICRO 2017.
- Tavakkol+, "MQSim: A Framework for Enabling Realistic Studies of Modern Multi-Queue SSD Devices," FAST 2018.
- Tavakkol+, "FLIN: Enabling Fairness and Enhancing Performance in Modern NVMe Solid State Drives," ISCA 2018.
- Sadrosadati+. "LTRF: Enabling High-Capacity Register Files for GPUs via Hardware/Software Cooperative Register Prefetching," ASPLOS 2018.

Charge vs. Resistive Memories

- Charge Memory (e.g., DRAM, Flash)
  - Write data by capturing charge Q
  - Read data by detecting voltage V

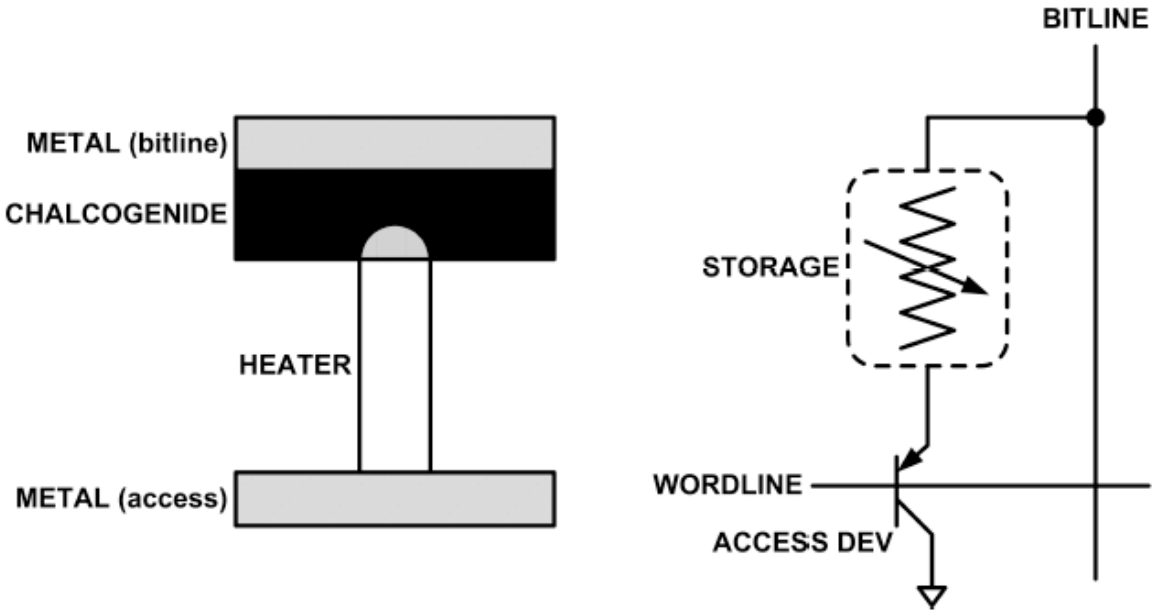
- Resistive Memory (e.g., PCM, STT-MRAM, memristors)
  - Write data by pulsing current dQ/dt
  - Read data by detecting resistance R

Promising Resistive Memory Technologies

- PCM
  - Inject current to change material phase
  - Resistance determined by phase
- STT-MRAM
  - Inject current to change magnet polarity
  - Resistance determined by polarity
- Memristors/RRAM/ReRAM
  - Inject current to change atomic structure
  - Resistance determined by atom distance

What is Phase Change Memory?

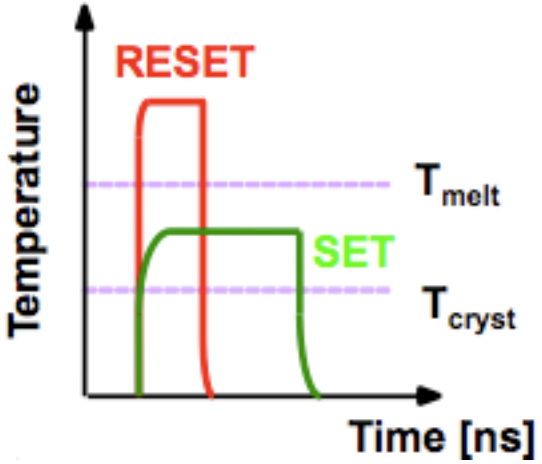
- Phase change material (chalcogenide glass) exists in two states:
  - Amorphous: Low optical reflexivity and high electrical resistivity
  - Crystalline: High optical reflexivity and low electrical resistivity

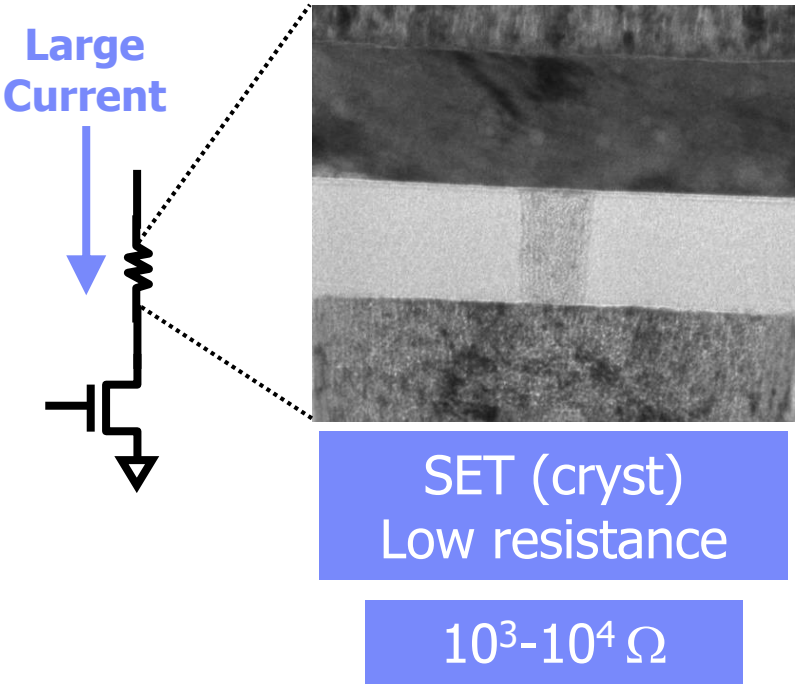


PCM is resistive memory: High resistance (0), Low resistance (1)
PCM cell can be switched between states reliably and quickly

How Does PCM Work?

- Write: change phase via current injection
  - SET: sustained current to heat cell above T*cryst*
  - RESET: cell heated above T*melt* and quenched
- Read: detect phase via material resistance
  - amorphous/crystalline





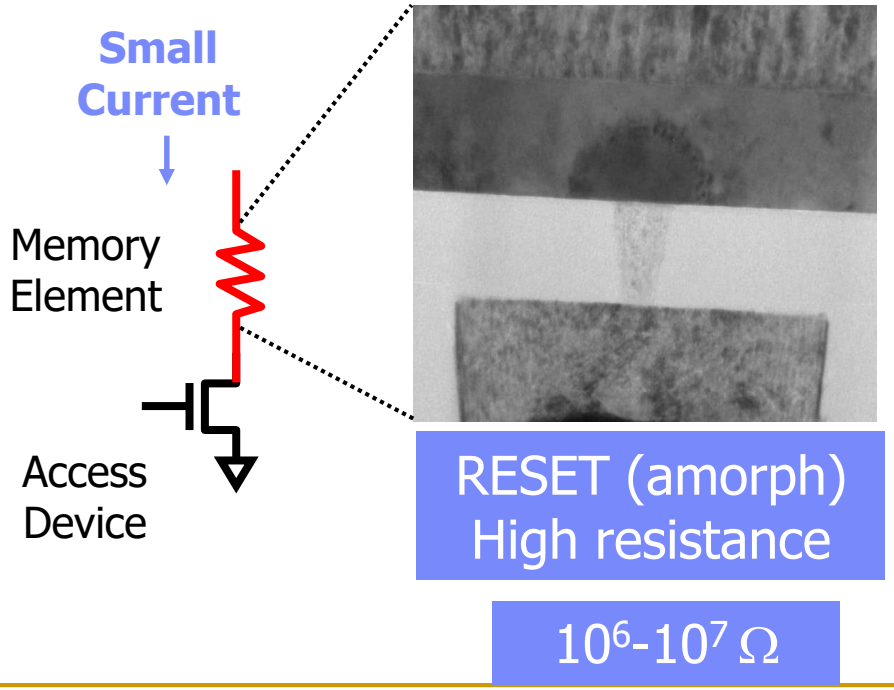
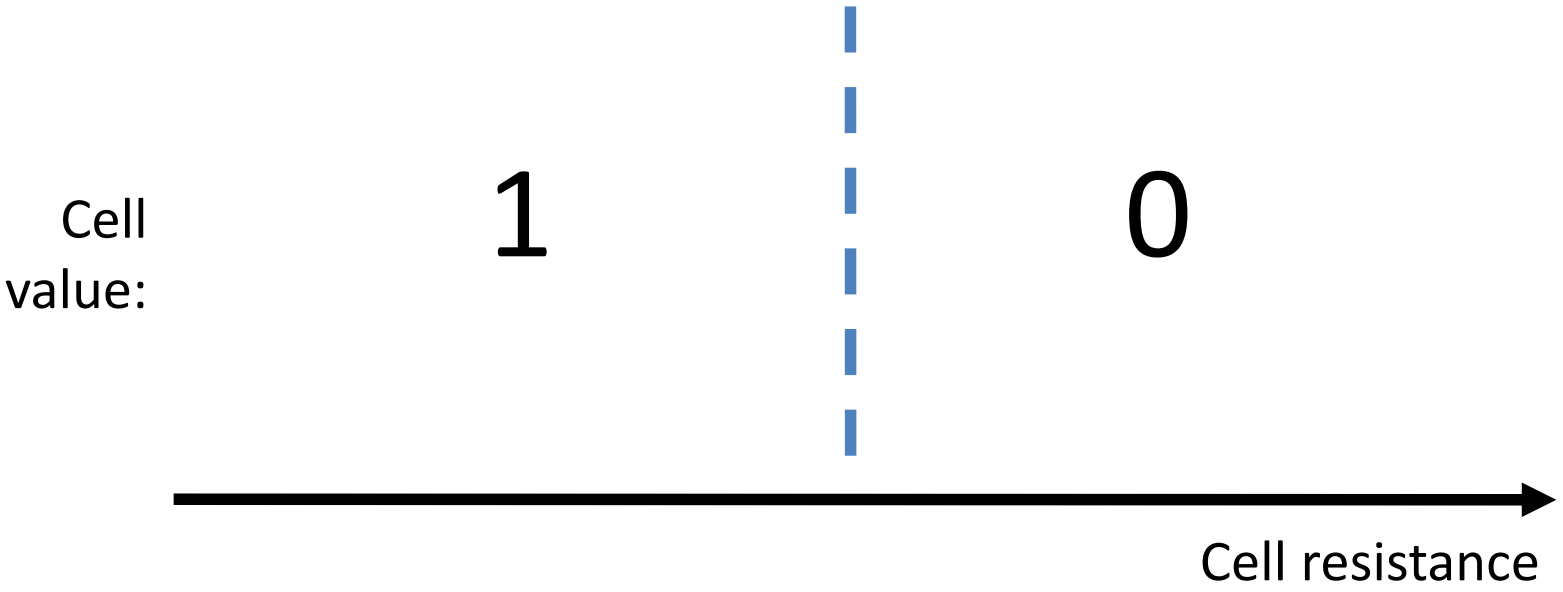


Photo Courtesy: Bipin Rajendran, IBM Slide Courtesy: Moinuddin Qureshi, IBM

Opportunity: PCM Advantages

- Scales better than DRAM, Flash
  - Requires current pulses, which scale linearly with feature size
  - Expected to scale to 9nm (2022 [ITRS])
  - Prototyped at 20nm (Raoux+, IBM JRD 2008)
- Can be denser than DRAM
  - Can store multiple bits per cell due to large resistance range
  - Prototypes with 2 bits/cell in ISSCC' 08, 4 bits/cell by 2012
- Non-volatile
  - Retain data for >10 years at 85C
- No refresh needed, low idle power

PCM Resistance → Value

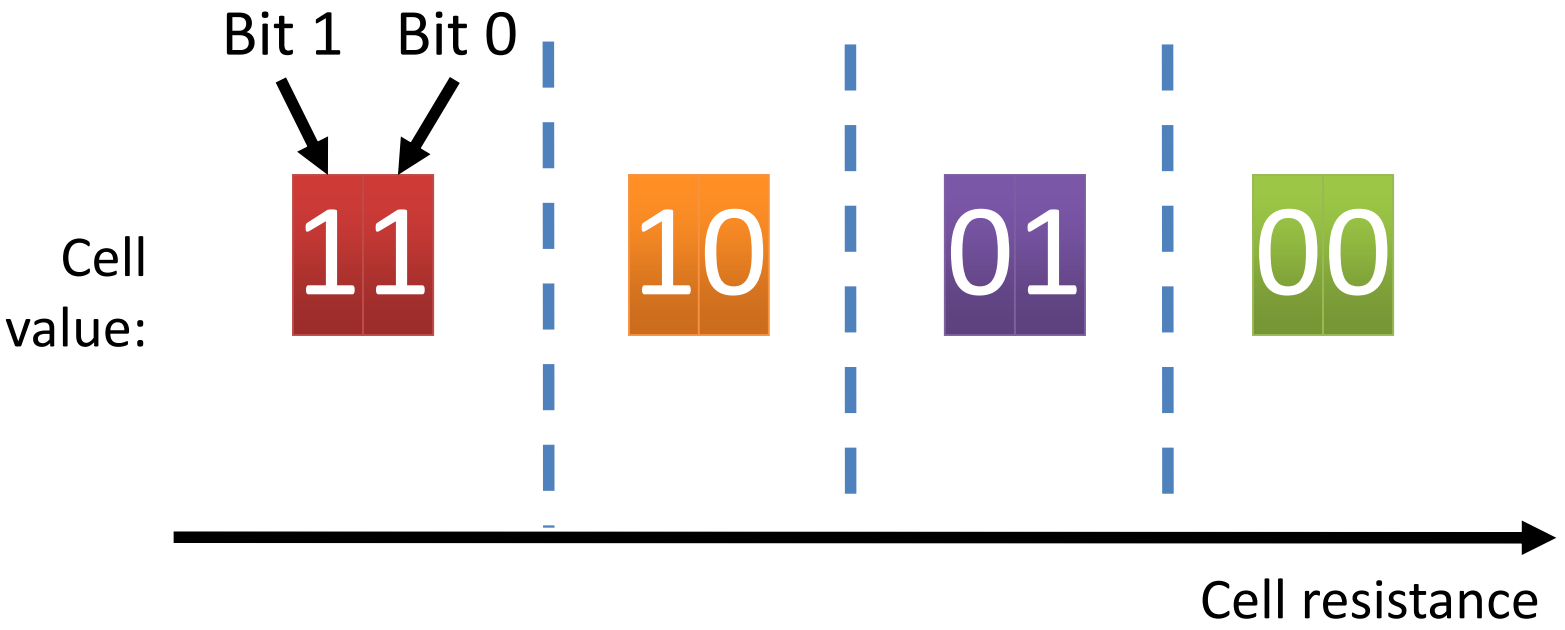


Multi-Level Cell PCM

- Multi-level cell: more than 1 bit per cell
  - Further increases density by 2 to 4x [Lee+,ISCA'09]

- But MLC-PCM also has drawbacks
  - Higher latency and energy than single-level cell PCM

MLC-PCM Resistance → Value

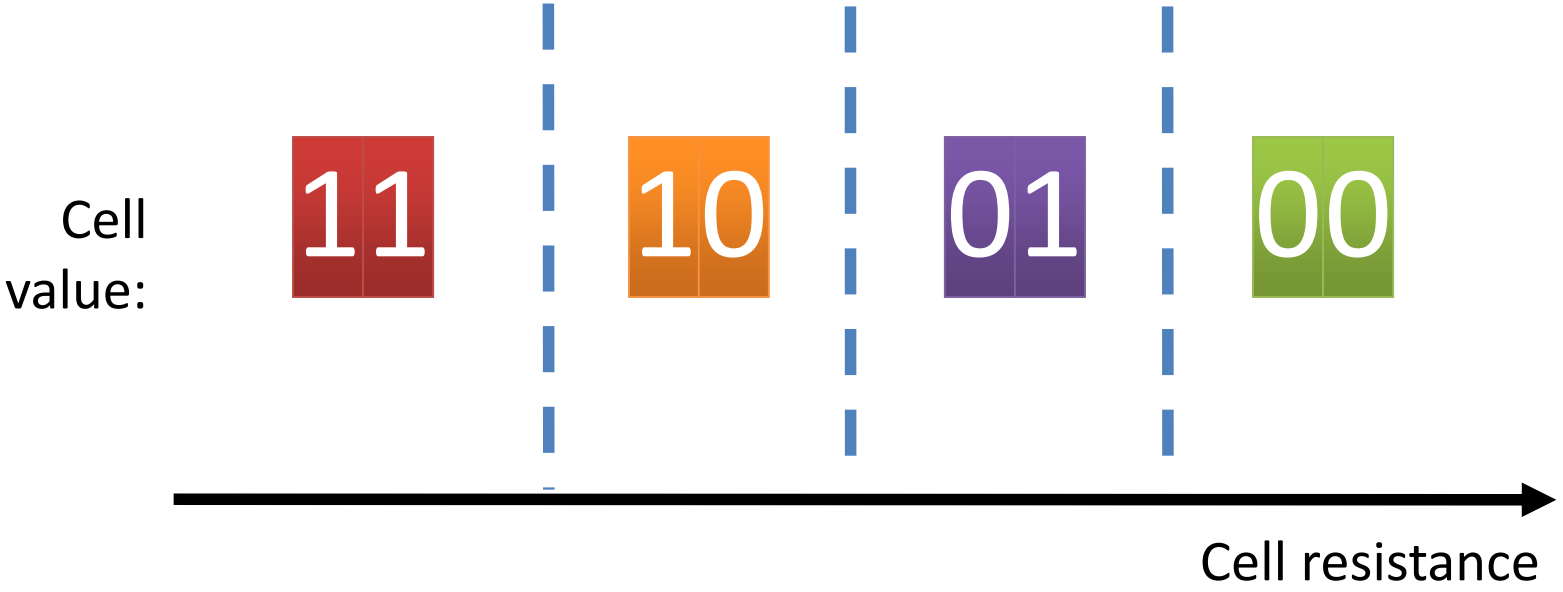


MLC-PCM Resistance → Value

Less margin between values

→ need more precise sensing/modification of cell contents

→ higher latency/energy (~2x for reads and 4x for writes)



Phase Change Memory Properties

- Surveyed prototypes from 2003-2008 (ITRS, IEDM, VLSI, ISSCC)
- Derived PCM parameters for F=90nm

- Lee, Ipek, Mutlu, Burger, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA 2009.
- Lee et al., "Phase Change Technology and the Future of Main Memory," IEEE Micro Top Picks 2010.

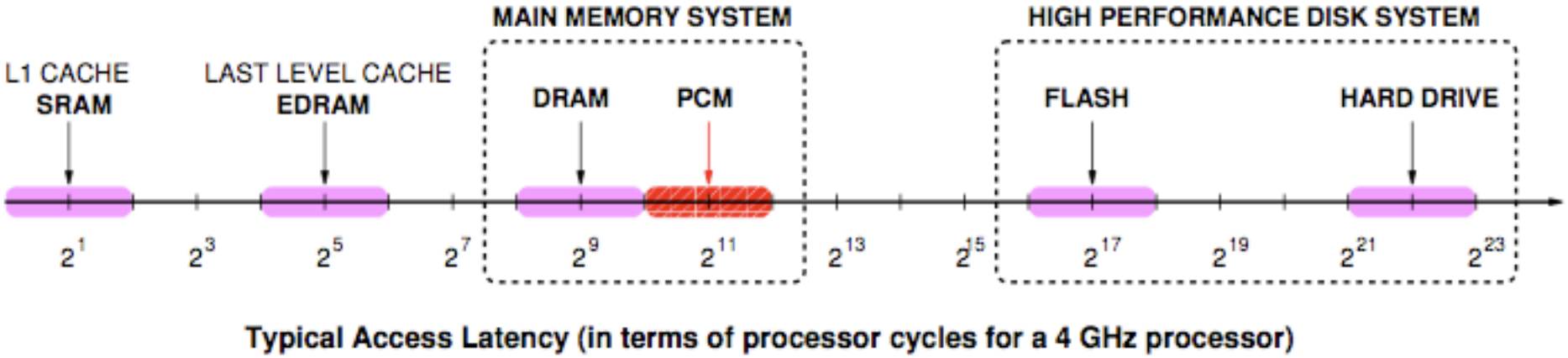
Table 1. Technology survey.

Parameter*	Published prototype									
	Horri[6]	Ahn[12]	Bedeschi[13]	Oh[14]	Pellizer[15]	Chen[5]	Kang[16]	Bedeschi[9]	Lee[10]	Lee[2]
Year	2003	2004	2004	2005	2006	2006	2006	2008	2008	**
Process, F (nm)	**	120	180	120	90	**	100	90	90	90
Array size (Mbytes)	**	64	8	64	**	**	256	256	512	**
Material	GST, N-d	GST, N-d	GST	GST	GST	GS, N-d	GST	GST	GST	GST, N-d
Cell size (μm^2)	**	0.290	0.290	**	0.097	60 nm^2	0.166	0.097	0.047	0.065 to 0.097
Cell size, F^2	**	20.1	9.0	**	12.0	**	16.6	12.0	5.8	9.0 to 12.0
Access device	**	**	BJT	FET	BJT	**	FET	BJT	Diode	BJT
Read time (ns)	**	70	48	68	**	**	62	**	55	48
Read current (μA)	**	**	40	**	**	**	**	**	**	40
Read voltage (V)	**	3.0	1.0	1.8	1.6	**	1.8	**	1.8	1.0
Read power (μW)	**	**	40	**	**	**	**	**	**	40
Read energy (pJ)	**	**	2.0	**	**	**	**	**	**	2.0
Set time (ns)	100	150	150	180	**	80	300	**	400	150
Set current (μA)	200	**	300	200	**	55	**	**	**	150
Set voltage (V)	**	**	2.0	**	**	1.25	**	**	**	1.2
Set power (μW)	**	**	300	**	**	34.4	**	**	**	90
Set energy (pJ)	**	**	45	**	**	2.8	**	**	**	13.5
Reset time (ns)	50	10	40	10	**	60	50	**	50	40
Reset current (μA)	600	600	600	600	400	90	600	300	600	300
Reset voltage (V)	**	**	2.7	**	1.8	1.6	**	1.6	**	1.6
Reset power (μW)	**	**	1620	**	**	80.4	**	**	**	480
Reset energy (pJ)	**	**	64.8	**	**	4.8	**	**	**	19.2
Write endurance (MLC)	10^7	10^9	10^6	**	10^8	10^4	**	10^5	10^5	10^8

* BJT: bipolar junction transistor; FET: field-effect transistor; GST: $Ge_2Sb_2Te_5$; MLC: multilevel cells; N-d: nitrogen doped.
** This information is not available in the publication cited.

Phase Change Memory Properties: Latency

- Latency comparable to, but slower than DRAM



Typical Access Latency (in terms of processor cycles for a 4 GHz processor)

- Read Latency
  - 50ns: 4x DRAM, 10^{-3}x NAND Flash
- Write Latency
  - 150ns: 12x DRAM
- Write Bandwidth
  - 5-10 MB/s: 0.1x DRAM, 1x NAND Flash

Qureshi+, "Scalable high performance main memory system using phase-change memory technology," ISCA 2009.

Phase Change Memory Properties

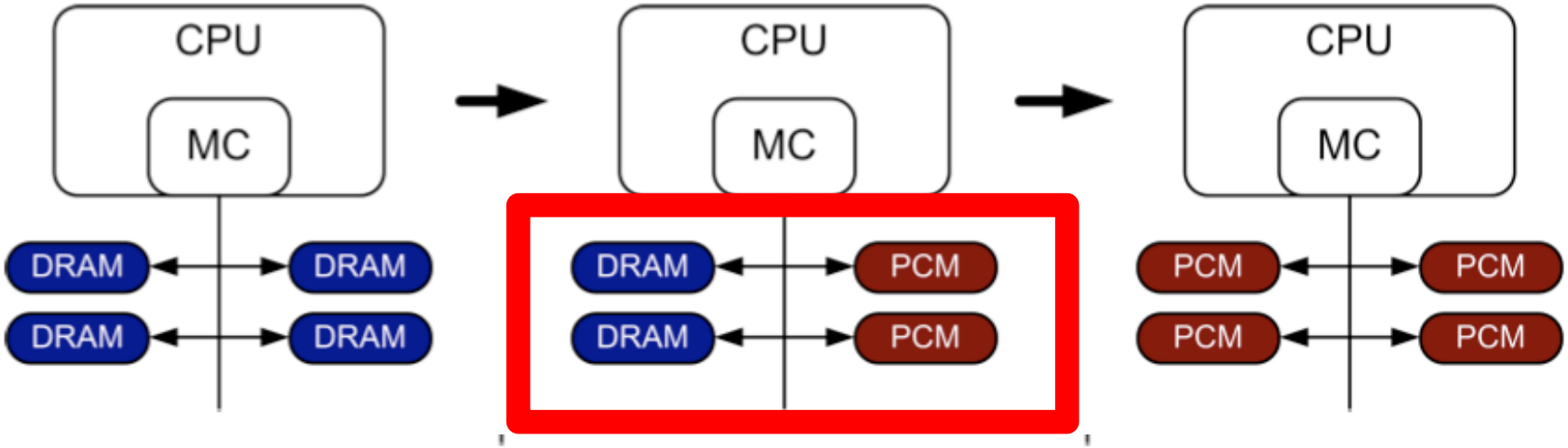
- Dynamic Energy
  - 40 uA Rd, 150 uA Wr
  - 2-43x DRAM, 1x NAND Flash
- Endurance
  - Writes induce phase change at 650C
  - Contacts degrade from thermal expansion/contraction
  - 10^8 writes per cell
  - 10^{-8}x DRAM, 10^3x NAND Flash
- Cell Size
  - 9-12F^2 using BJT, single-level cells
  - 1.5x DRAM, 2-3x NAND (will scale with feature size, MLC)

Phase Change Memory: Pros and Cons

- Pros over DRAM
  - Better technology scaling (capacity and cost)
  - Non volatile → Persistent
  - Low idle power (no refresh)
- Cons
  - Higher latencies: ~4-15x DRAM (especially write)
  - Higher active energy: ~2-50x DRAM (especially write)
  - Lower endurance (a cell dies after ~10^8 writes)
  - Reliability issues (resistance drift)
- Challenges in enabling PCM as DRAM replacement/helper:
  - Mitigate PCM shortcomings
  - Find the right way to place PCM in the system

PCM-based Main Memory (I)

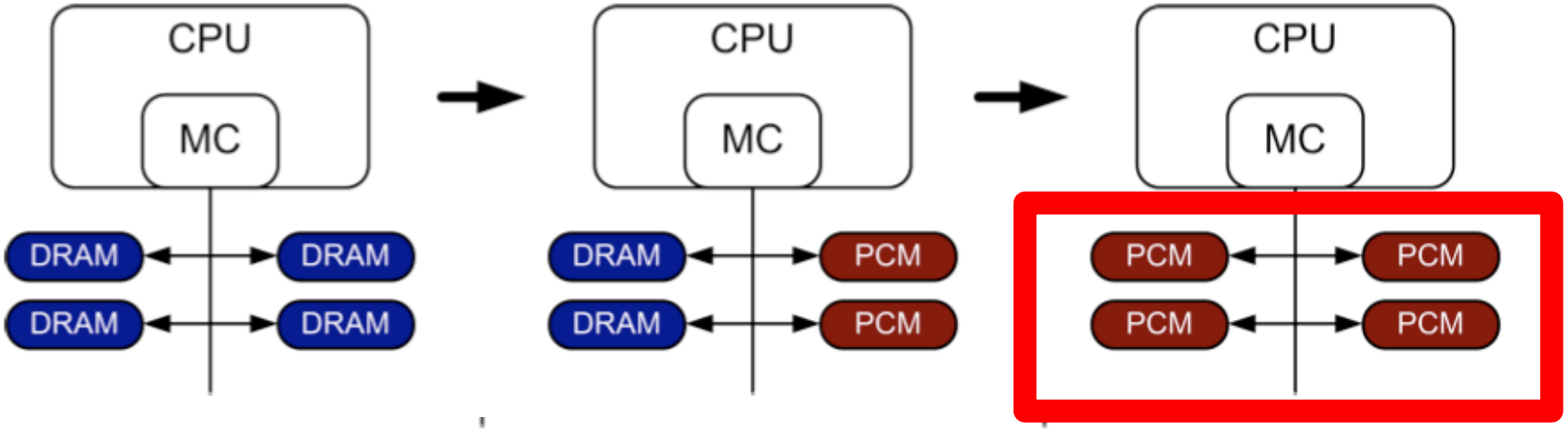
- How should PCM-based (main) memory be organized?



- Hybrid PCM+DRAM [Qureshi+ ISCA'09, Dhiman+ DAC'09]:
  - How to partition/migrate data between PCM and DRAM

PCM-based Main Memory (II)

- How should PCM-based (main) memory be organized?



- Pure PCM main memory [Lee et al., ISCA'09, Top Picks'10]:
  - How to redesign entire hierarchy (and cores) to overcome PCM shortcomings

An Initial Study: Replace DRAM with PCM

- Lee, Ipek, Mutlu, Burger, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA 2009.
  - Surveyed prototypes from 2003-2008 (e.g. IEDM, VLSI, ISSCC)
  - Derived "average" PCM parameters for F=90nm

Density

- 9 - 12F^2 using BJT
- 1.5× DRAM

Latency

- 50ns Rd, 150ns Wr
- 4×, 12× DRAM

Endurance

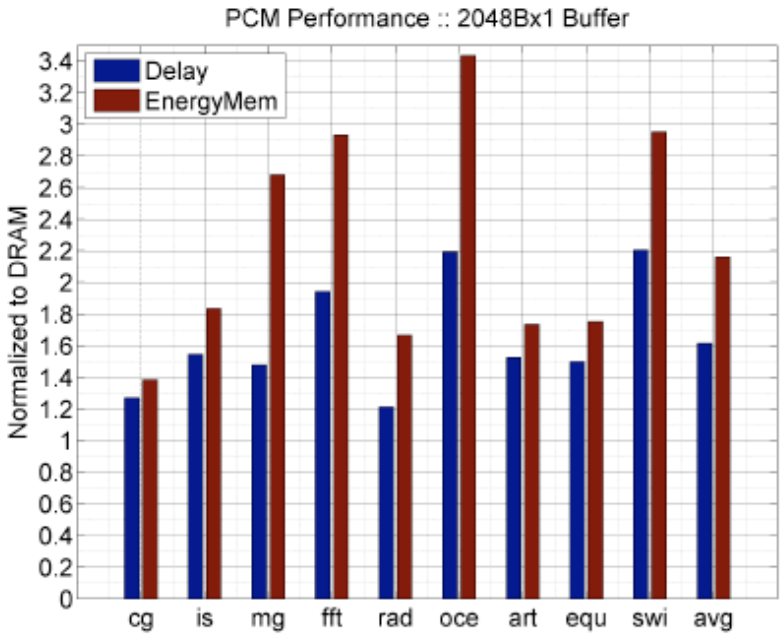
- 1E+08 writes
- 1E-08× DRAM

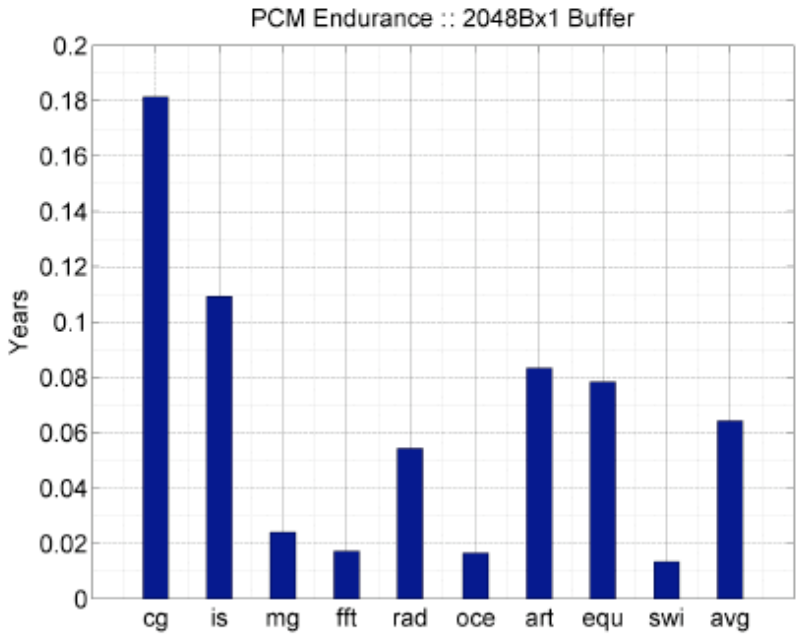
Energy

- 40μA Rd, 150μA Wr
- 2×, 43× DRAM

Results: Naïve Replacement of DRAM with PCM

- Replace DRAM with PCM in a 4-core, 4MB L2 system
- PCM organized the same as DRAM: row buffers, banks, peripherals
- 1.6x delay, 2.2x energy, 500-hour average lifetime



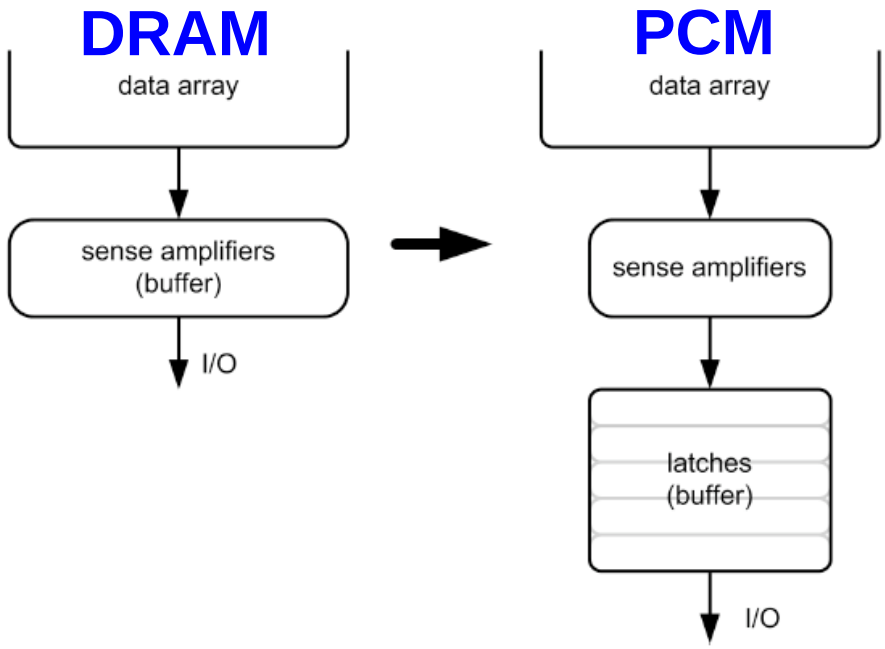


- Lee, Ipek, Mutlu, Burger, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA 2009.

Architecting PCM to Mitigate Shortcomings

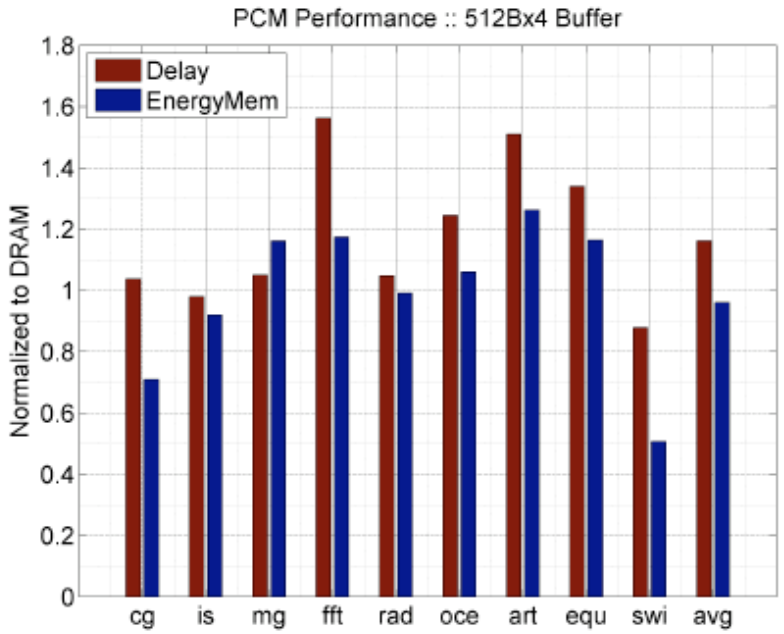
- Idea 1: Use multiple narrow row buffers in each PCM chip
  → Reduces array reads/writes → better endurance, latency, energy

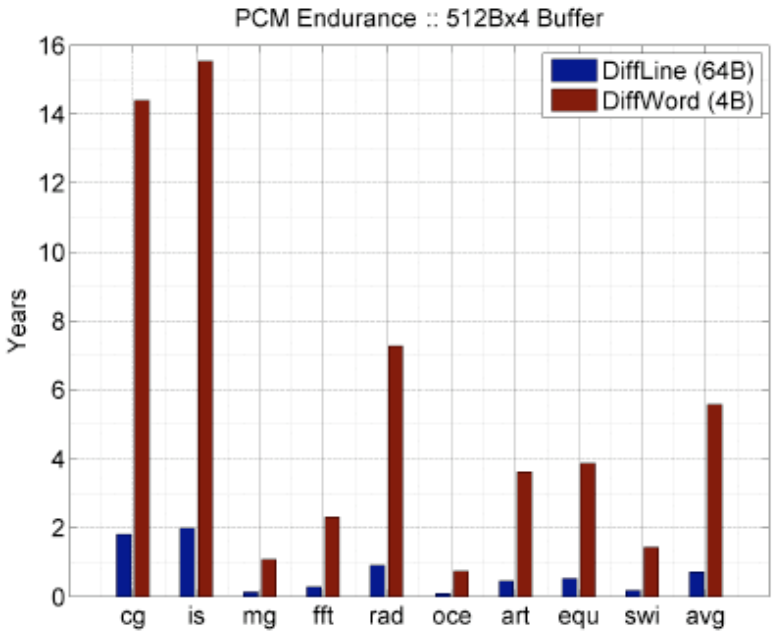
- Idea 2: Write into array at cache block or word granularity
  → Reduces unnecessary wear



Results: Architected PCM as Main Memory

- 1.2x delay, 1.0x energy, 5.6-year average lifetime
- Scaling improves energy, endurance, density

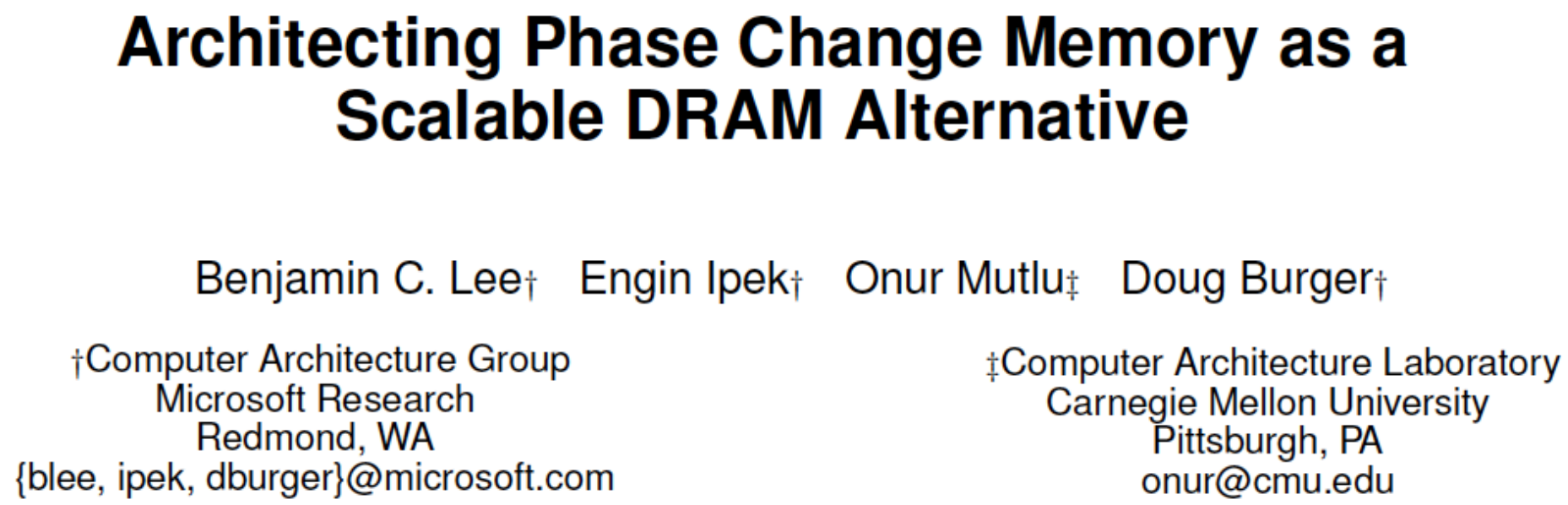




- Caveat 1: Worst-case lifetime is much shorter (no guarantees)
- Caveat 2: Intensive applications see large performance and energy hits
- Caveat 3: Optimistic PCM parameters?

Required Reading: PCM As Main Memory

- Benjamin C. Lee, Engin Ipek, Onur Mutlu, and Doug Burger, **"Architecting Phase Change Memory as a Scalable DRAM Alternative"**
  *Proceedings of the 36th International Symposium on Computer Architecture (**ISCA**)*, pages 2-13, Austin, TX, June 2009. Slides (pdf)



Architecting Phase Change Memory as a Scalable DRAM Alternative

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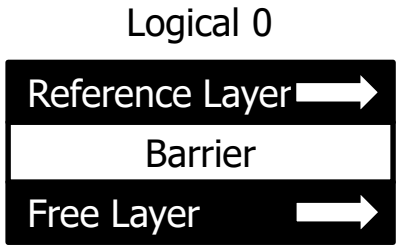
More on PCM As Main Memory (II)

- Benjamin C. Lee, Ping Zhou, Jun Yang, Youtao Zhang, Bo Zhao, Engin Ipek, Onur Mutlu, and Doug Burger, **"Phase Change Technology and the Future of Main Memory"** *IEEE Micro, Special Issue: Micro's Top Picks from 2009 Computer Architecture Conferences (**MICRO TOP PICKS**)*, Vol. 30, No. 1, pages 60-70, January/February 2010.

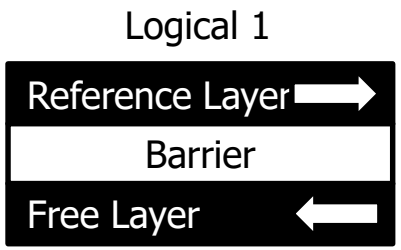
PHASE-CHANGE TECHNOLOGY AND THE FUTURE OF MAIN MEMORY

STT-MRAM as Main Memory

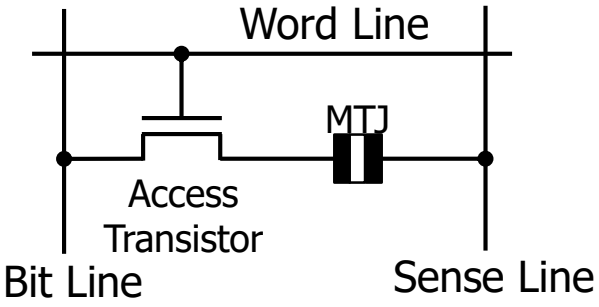
- Magnetic Tunnel Junction (MTJ) device
  - Reference layer: Fixed magnetic orientation
  - Free layer: Parallel or anti-parallel



- Magnetic orientation of the free layer determines logical state of device
  - High vs. low resistance



- Write: Push large current through MTJ to change orientation of free layer
- Read: Sense current flow



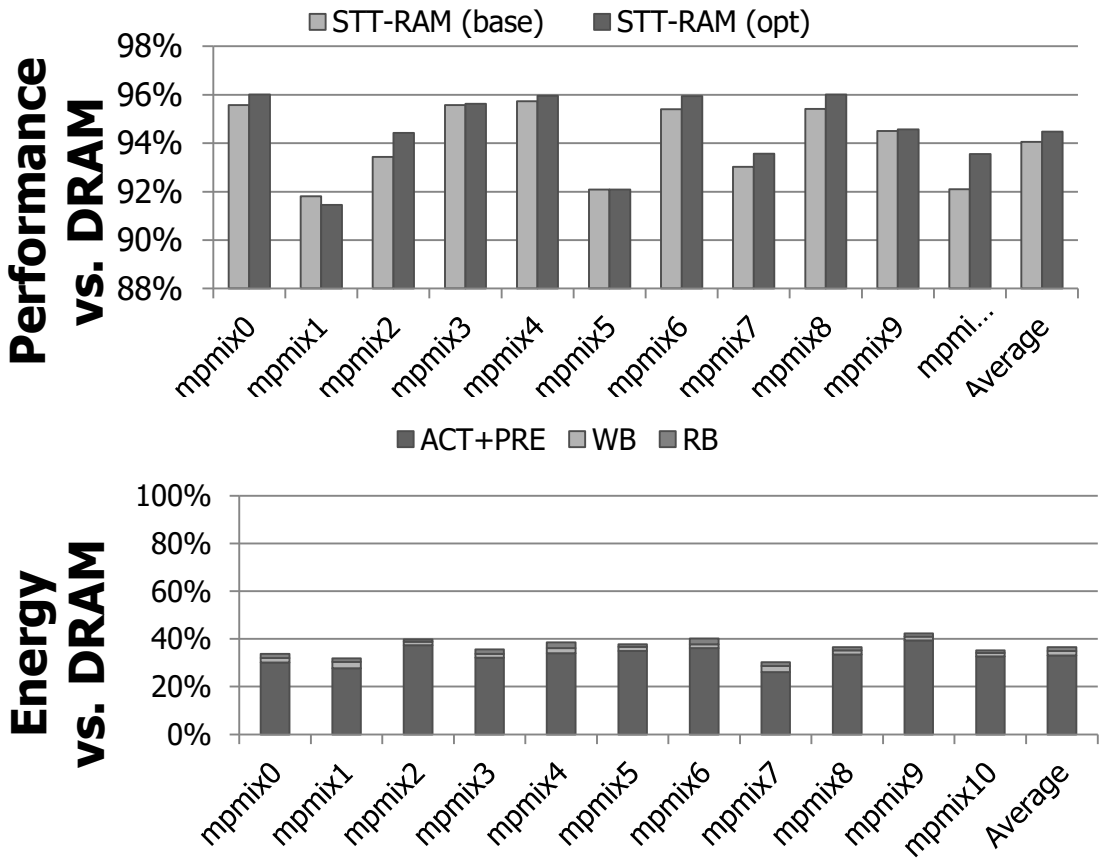
- Kultursay et al., "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.

STT-MRAM: Pros and Cons

- Pros over DRAM
  - Better technology scaling (capacity and cost)
  - Non volatile → Persistent
  - Low idle power (no refresh)
- Cons
  - Higher write latency
  - Higher write energy
  - Poor density (currently)
  - Reliability?
- Another level of freedom
  - Can trade off non-volatility for lower write latency/energy (by reducing the size of the MTJ)

Architected STT-MRAM as Main Memory

- 4-core, 4GB main memory, multiprogrammed workloads
- ~6% performance loss, ~60% energy savings vs. DRAM



Kultursay+, "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.

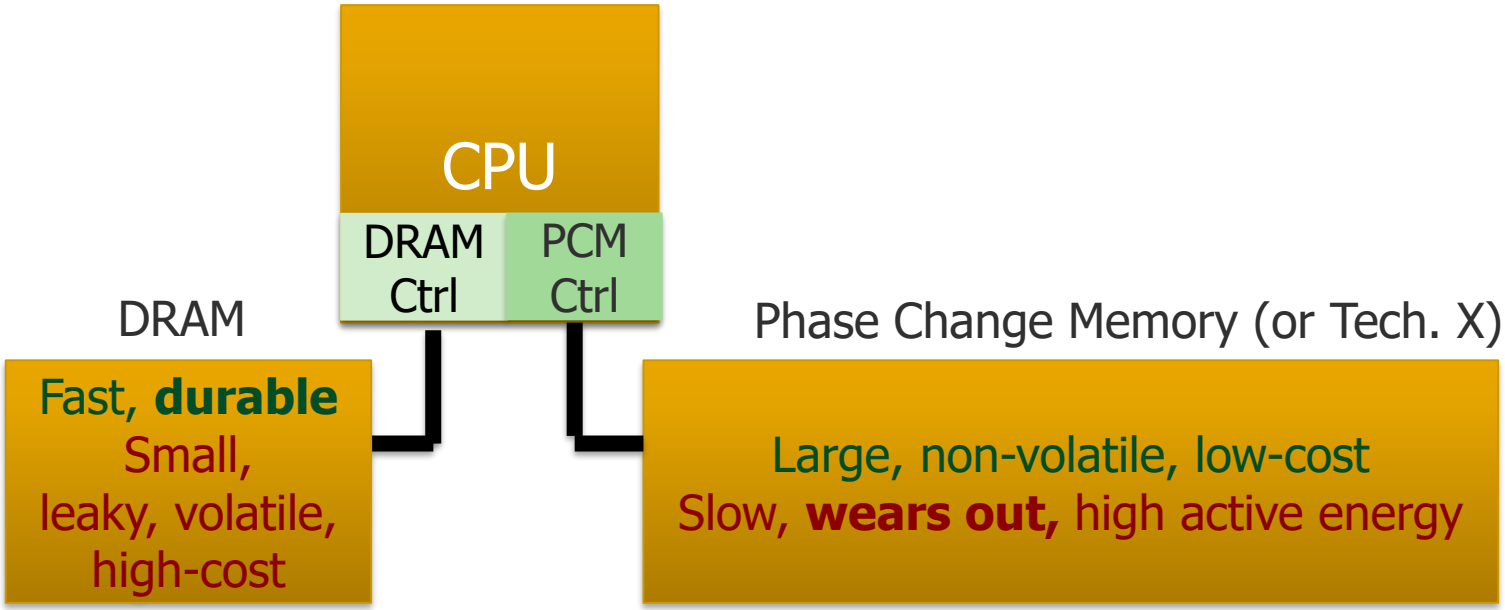
More on STT-MRAM as Main Memory

- Emre Kultursay, Mahmut Kandemir, Anand Sivasubramaniam, and Onur Mutlu,
  "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative"
  Proceedings of the 2013 IEEE International Symposium on Performance Analysis of Systems and Software (***ISPASS***), Austin, TX, April 2013. Slides (pptx) (pdf)

Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative

Emre Kültürsay*, Mahmut Kandemir*, Anand Sivasubramaniam*, and Onur Mutlu†
*The Pennsylvania State University and †Carnegie Mellon University

A More Viable Approach: Hybrid Memory Systems



Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.

Yoon+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

Challenge and Opportunity

Providing the Best of Multiple Metrics

with

Multiple Memory Technologies

Challenge and Opportunity

Heterogeneous,
Configurable,
Programmable
Memory Systems

Hybrid Memory Systems: Issues

- Cache vs. Main Memory
- Granularity of Data Move/Manage-ment: Fine or Coarse
- Hardware vs. Software vs. HW/SW Cooperative
- When to migrate data?
- How to design a scalable and efficient large cache?
- …

One Option: DRAM as a Cache for PCM

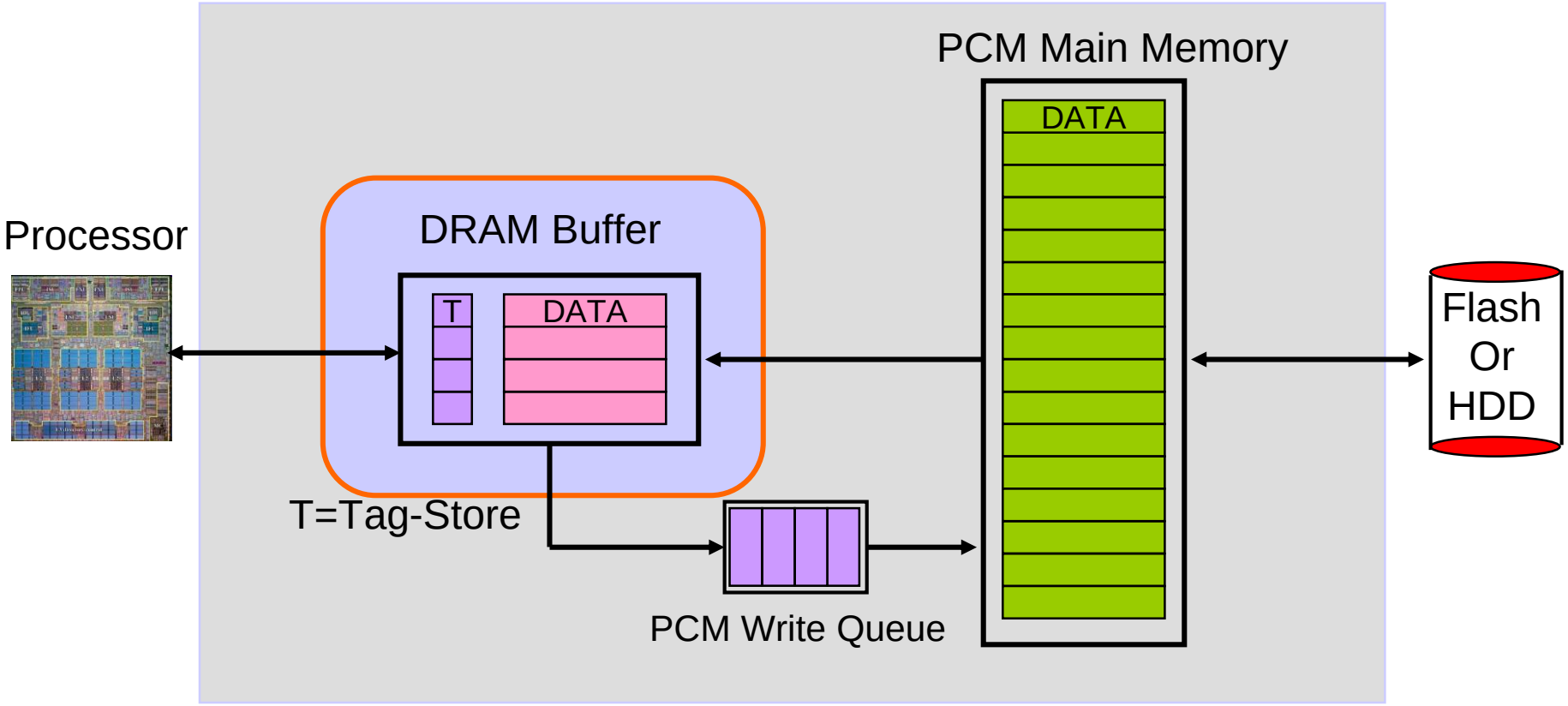
- PCM is main memory; DRAM caches memory rows/blocks
  - Benefits: Reduced latency on DRAM cache hit; write filtering
- Memory controller hardware manages the DRAM cache
  - Benefit: Eliminates system software overhead

- Three issues:
  - What data should be placed in DRAM versus kept in PCM?
  - What is the granularity of data movement?
  - How to design a low-cost hardware-managed DRAM cache?

- Two idea directions:
  - Locality-aware data placement **[Yoon+ , ICCD 2012]**
  - Cheap tag stores and dynamic granularity **[Meza+, IEEE CAL 2012]**

DRAM as a Cache for PCM

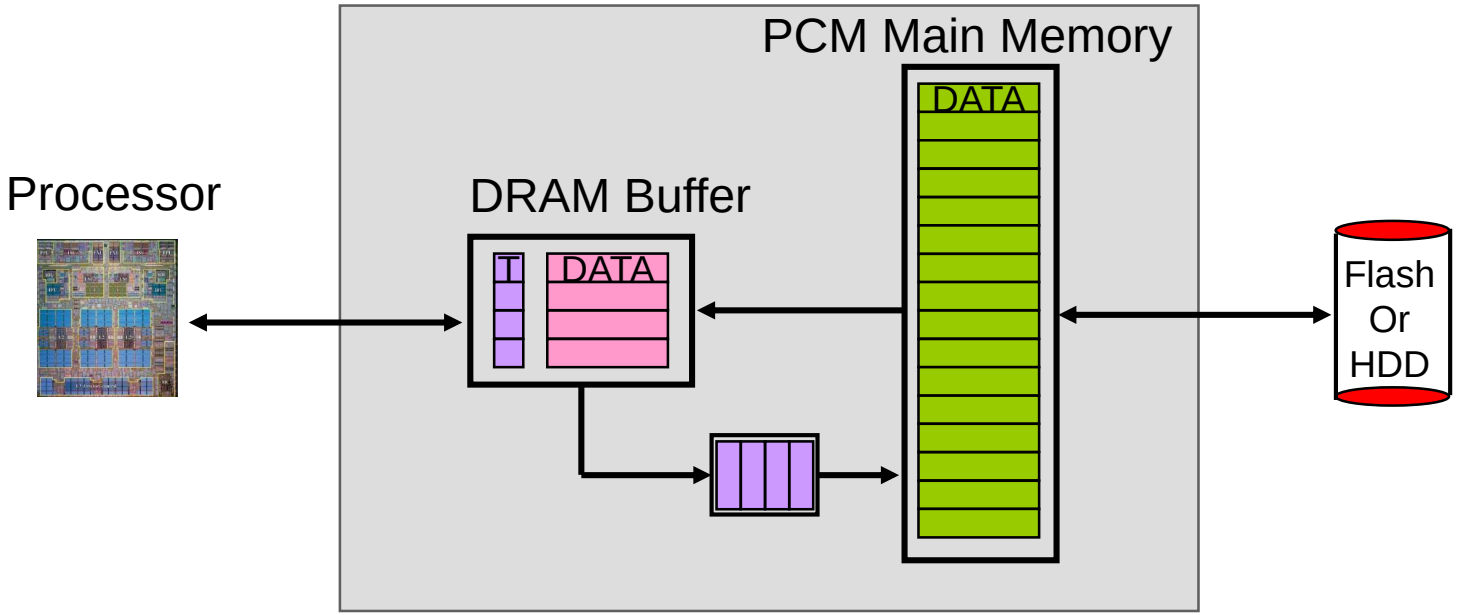
- Goal: Achieve the best of both DRAM and PCM/NVM
  - Minimize amount of DRAM w/o sacrificing performance, endurance
  - DRAM as cache to tolerate PCM latency and write bandwidth
  - PCM as main memory to provide large capacity at good cost and power



Qureshi+, "Scalable high performance main memory system using phase-change memory technology," ISCA 2009.

Write Filtering Techniques

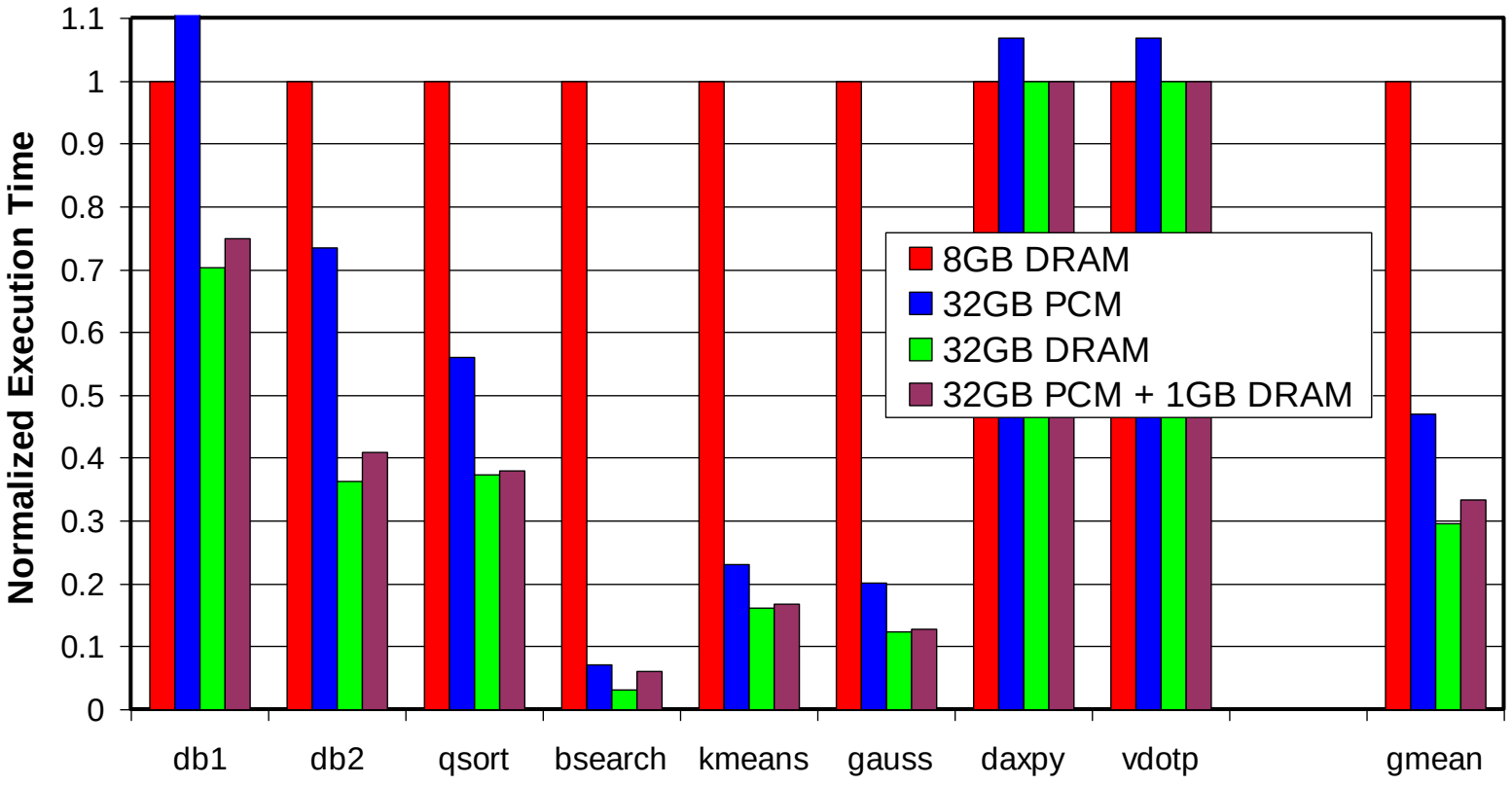
- Lazy Write: Pages from disk installed only in DRAM, not PCM
- Partial Writes: Only dirty lines from DRAM page written back
- Page Bypass: Discard pages with poor reuse on DRAM eviction



- Qureshi et al., "Scalable high performance main memory system using phase-change memory technology," ISCA 2009.

Results: DRAM as PCM Cache (I)

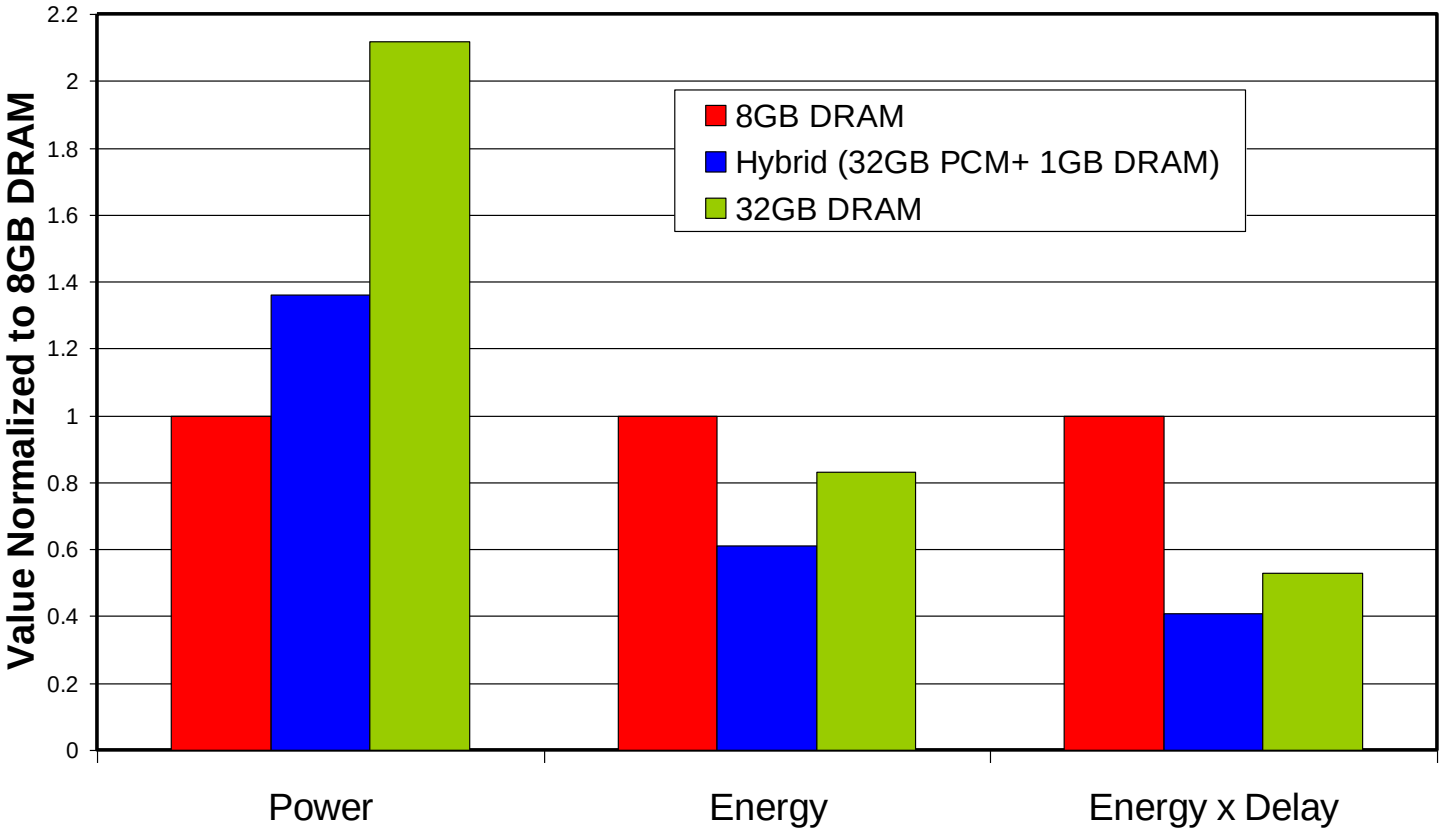
- Simulation of 16-core system, 8GB DRAM main-memory at 320 cycles, HDD (2 ms) with Flash (32 us) with Flash hit-rate of 99%
- Assumption: PCM 4x denser, 4x slower than DRAM
- DRAM block size = PCM page size (4kB)



Qureshi+, "Scalable high performance main memory system using phase-change memory technology," ISCA 2009.

Results: DRAM as PCM Cache (II)

- PCM-DRAM Hybrid performs similarly to similar-size DRAM
- Significant energy savings with PCM-DRAM Hybrid
- Average lifetime: 9.7 years (no guarantees)



Qureshi+, "Scalable high performance main memory system using phase-change memory technology," ISCA 2009.

More on DRAM-PCM Hybrid Memory

- **Scalable High-Performance Main Memory System Using Phase-Change Memory Technology.**
  Moinuddin K. Qureshi, Viji Srinivasan, and Jude A. Rivers
  Appears in the International Symposium on Computer Architecture (ISCA) 2009.

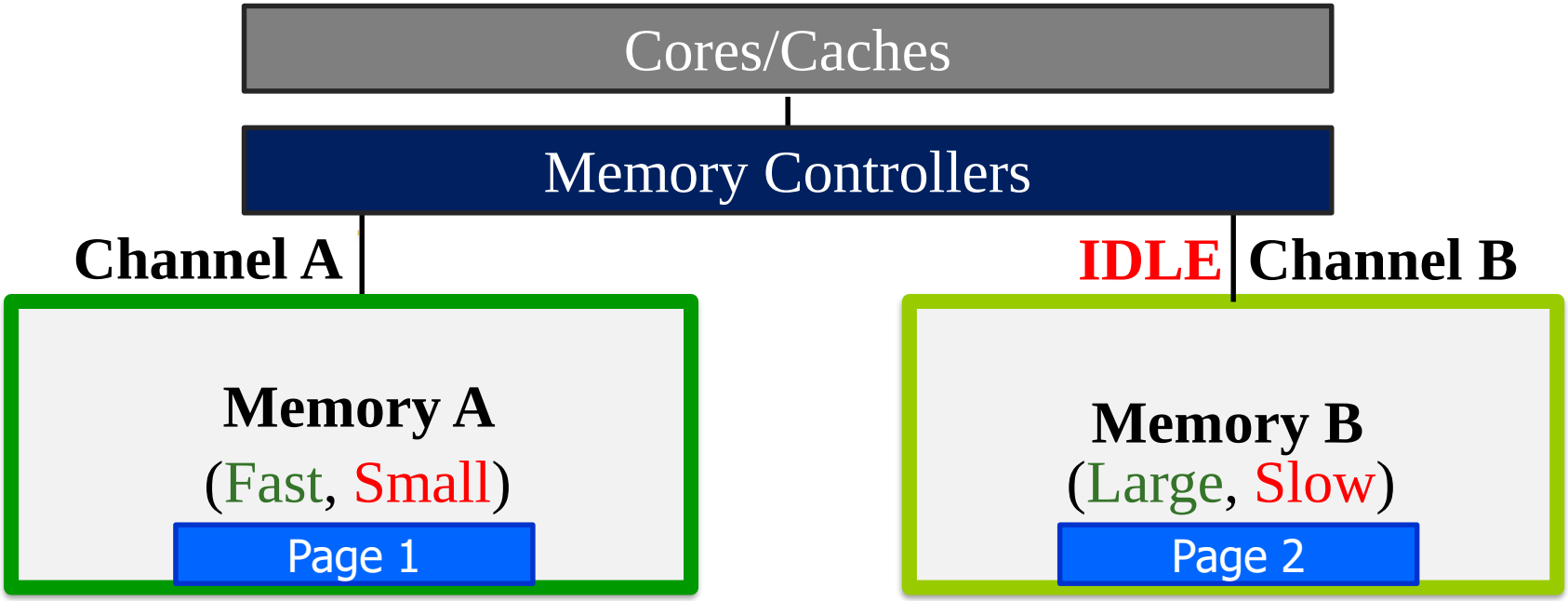
Scalable High Performance Main Memory System Using Phase-Change Memory Technology

Moinuddin K. Qureshi Vijayalakshmi Srinivasan Jude A. Rivers

IBM Research
T. J. Watson Research Center, Yorktown Heights NY 10598

{mkquresh, viji, jarivers}@us.ibm.com

Data Placement in Hybrid Memory



Which memory do we place each page in, to **maximize system performance**?

- Memory A is fast, but small
- Load should be balanced on both channels?
- Page migrations have performance and energy overhead

Data Placement Between DRAM and PCM

- Idea: Characterize data access patterns and guide data placement in hybrid memory
- Streaming accesses: As fast in PCM as in DRAM
- Random accesses: Much faster in DRAM
- Idea: Place random access data with some reuse in DRAM; streaming data in PCM
- Yoon+, "Row Buffer Locality-Aware Data Placement in Hybrid Memories," ICCD 2012 Best Paper Award.

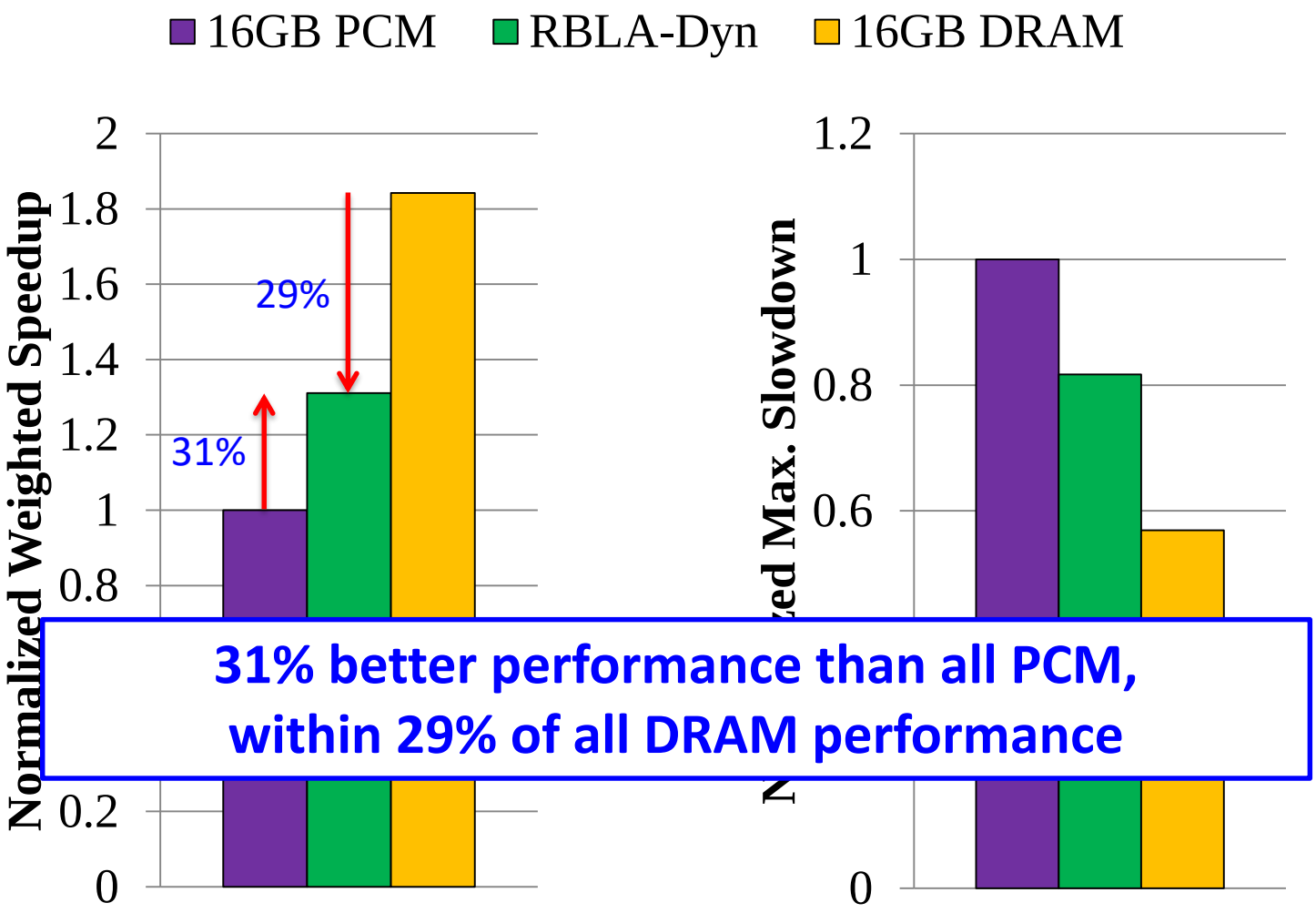
Key Observation & Idea

- Row buffers exist in both DRAM and PCM
  - Row hit latency **similar** in DRAM & PCM [Lee+ ISCA'09]
  - Row miss latency **small** in DRAM, **large** in PCM

- Place data in DRAM which
  - is likely to miss in the row buffer (low row buffer locality)→ miss penalty is smaller in DRAM

    AND
  - is reused many times → cache only the data worth the movement cost and DRAM space

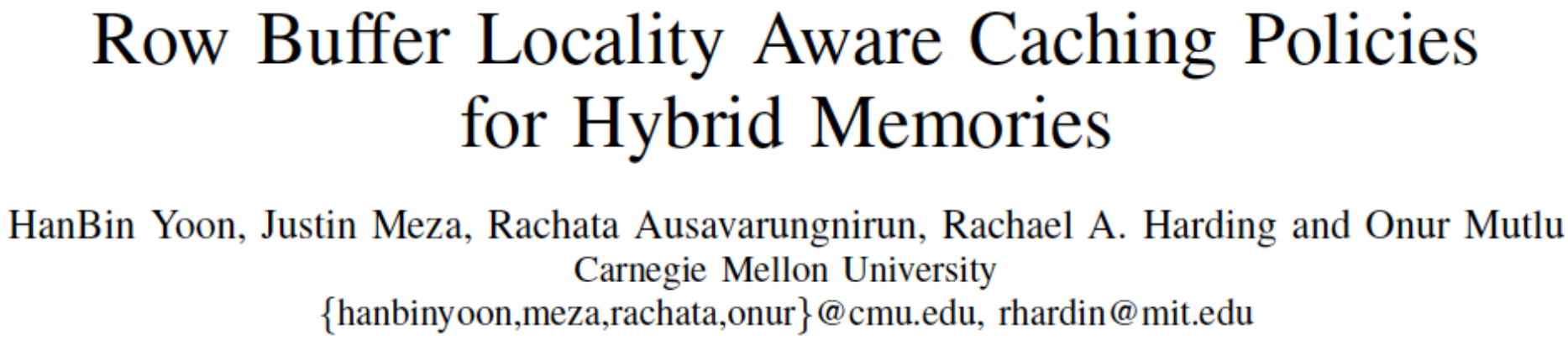
Hybrid vs. All-PCM/DRAM [ICCD'12]



Yoon+, "Row Buffer Locality-Aware Data Placement in Hybrid Memories," ICCD 2012 Best Paper Award.

More on Hybrid Memory Data Placement

- HanBin Yoon, Justin Meza, Rachata Ausavarungnirun, Rachael Harding, and Onur Mutlu,
  "Row Buffer Locality Aware Caching Policies for Hybrid Memories"
  *Proceedings of the 30th IEEE International Conference on Computer Design (**ICCD**)*, Montreal, Quebec, Canada, September 2012. Slides (pptx) (pdf)



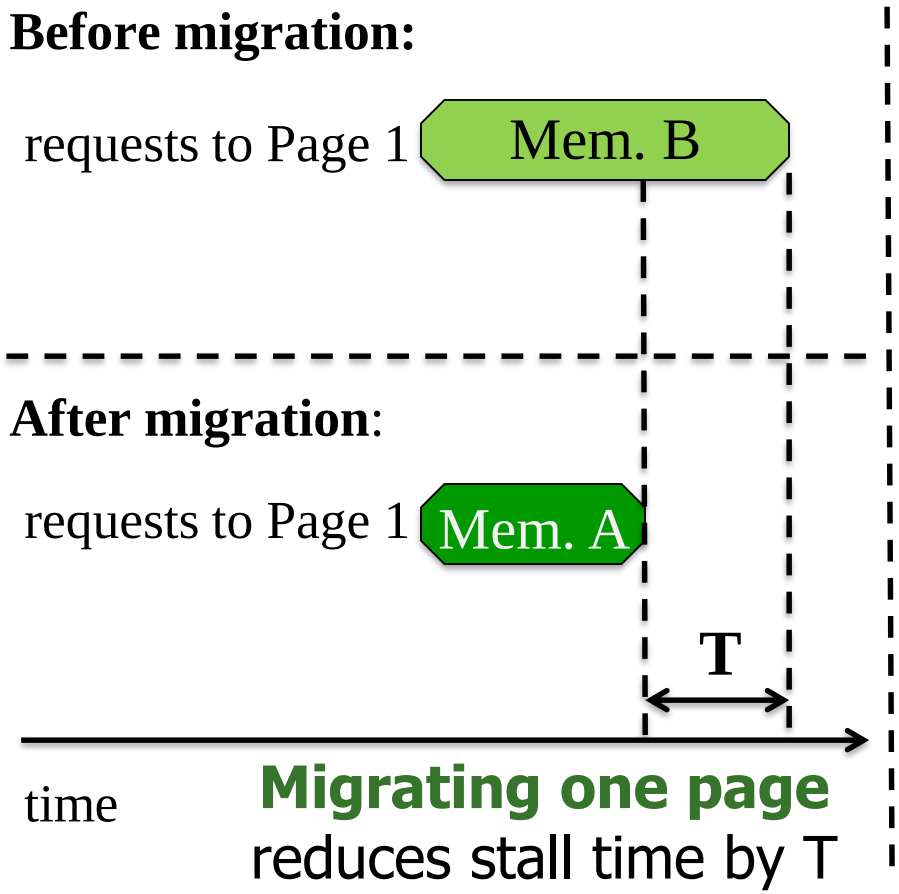
Row Buffer Locality Aware Caching Policies for Hybrid Memories

HanBin Yoon, Justin Meza, Rachata Ausavarungnirun, Rachael A. Harding and Onur Mutlu
Carnegie Mellon University
{hanbinyoon,meza,rachata,onur}@cmu.edu, rhardin@mit.edu

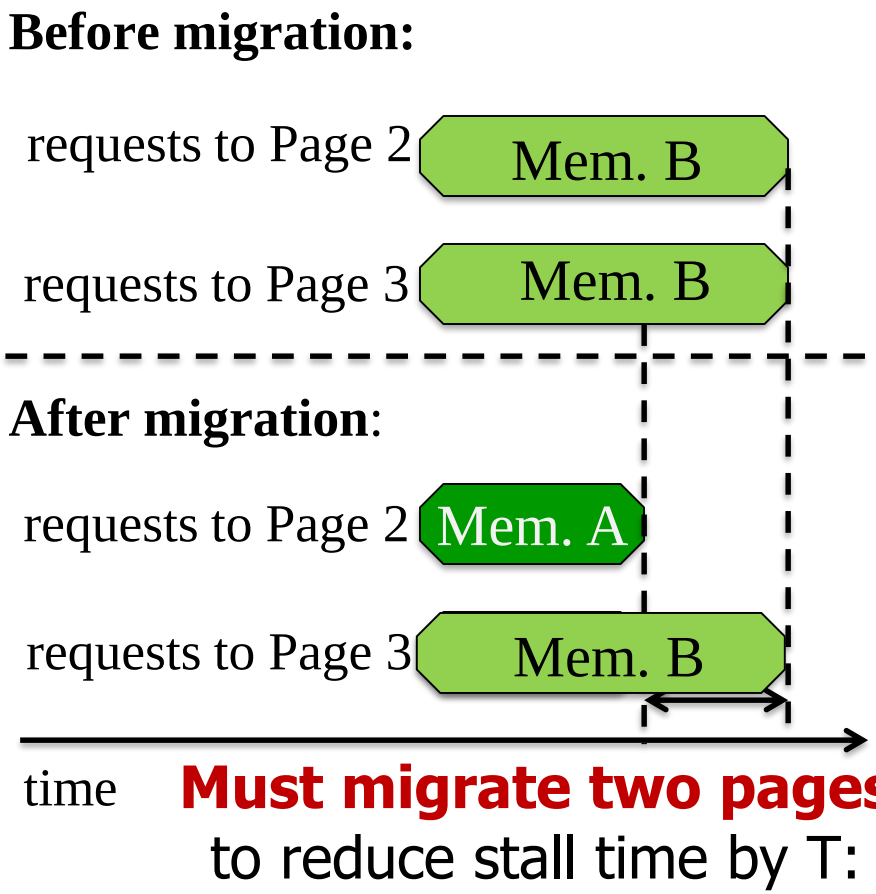
Weaknesses of Existing Solutions

- They are all heuristics that consider only a ***limited part*** **of memory access behavior**
- **Do not *directly* capture the overall system performance impact** of data placement decisions
- Example: None capture **memory-level parallelism** (MLP)
  - Number of ***concurrent*** **memory requests** from the same application when a page is accessed
  - Affects how much page migration helps performance

Importance of Memory-Level Parallelism



Migrating one page
reduces stall time by T



Must migrate two pages
to reduce stall time by T:
migrating one page alone
does not help

Page migration decisions **need to consider MLP**

Our Goal [CLUSTER 2017]

A **generalized** mechanism that

1. Directly estimates the **performance benefit of migrating a page** between **any two types of memory**

2. Places **only** the **performance-critical data** in the fast memory

Utility-Based Hybrid Memory Management

- A memory manager that works for ***any*** hybrid memory
  - e.g., DRAM-NVM, DRAM-RLDRAM

- **Key Idea**
  - For each page, use **comprehensive** characteristics to calculate estimated ***utility*** (i.e., performance impact) of migrating page from one memory to the other in the system
  - **Migrate only pages with the highest utility** (i.e., pages that improve system performance the most when migrated)

- Li+, "Utility-Based Hybrid Memory Management", CLUSTER 2017.

Key Mechanisms of UH-MEM

- For each page, estimate **utility** using a **performance model**
  - **Application stall time reduction**

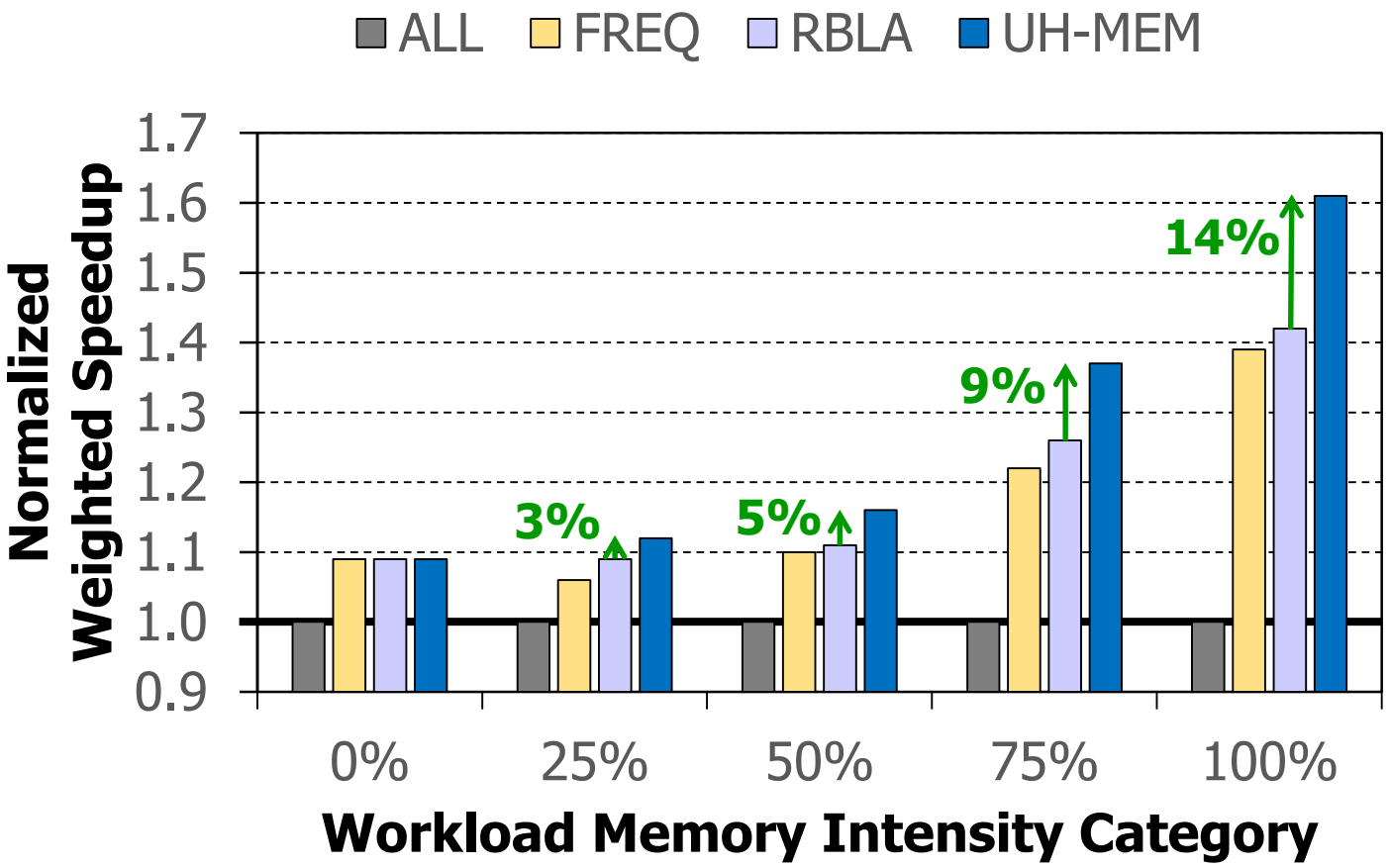
    How much would migrating a page benefit the performance of the application that the page belongs to?
  - **Application performance sensitivity**

    How much does the improvement of a single application's performance increase the *overall* system performance?

$$Utility = \Delta StallTime_i \times Sensitivity_i$$

- **Migrate** only pages whose utility exceed the migration threshold from slow memory to fast memory
- Periodically **adjust migration threshold**

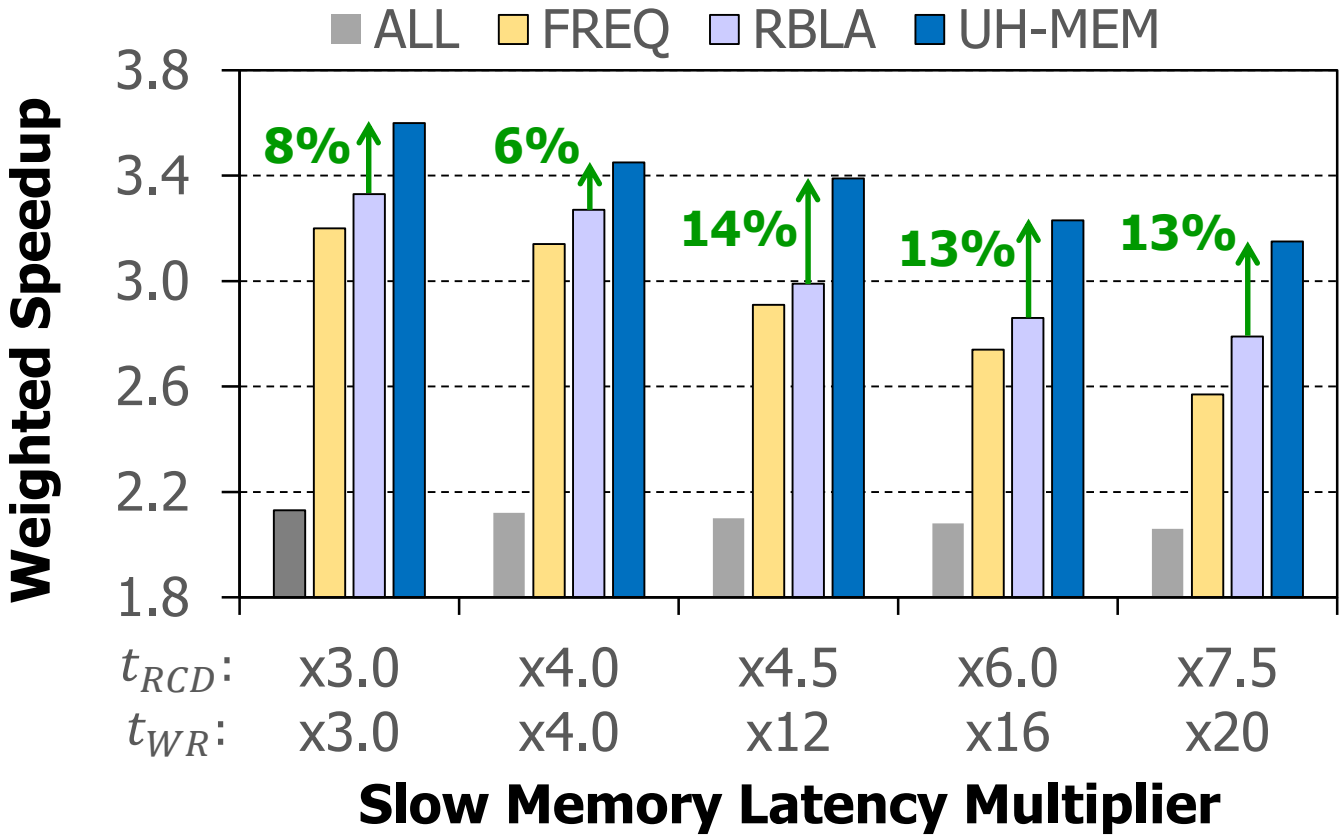
Results: System Performance



UH-MEM improves system performance
over the best state-of-the-art hybrid memory manager

Results: Sensitivity to Slow Memory Latency

- We vary t_{RCD} and t_{WR} of the slow memory



UH-MEM improves system performance for a wide variety of hybrid memory systems

More on UH-MEM

- Yang Li, Saugata Ghose, Jongmoo Choi, Jin Sun, Hui Wang, and Onur Mutlu,
  "Utility-Based Hybrid Memory Management"
  Proceedings of the 19th IEEE Cluster Conference (***CLUSTER***), Honolulu, Hawaii, USA, September 2017.
  [Slides (pptx) (pdf)]

Utility-Based Hybrid Memory Management

Yang Li† Saugata Ghose† Jongmoo Choi‡ Jin Sun† Hui Wang⋆ Onur Mutlu†‡
†*Carnegie Mellon University* ‡*Dankook University* ⋆*Beihang University* †*ETH Zürich*

Challenge and Opportunity

Enabling
an Emerging Technology
to Augment DRAM

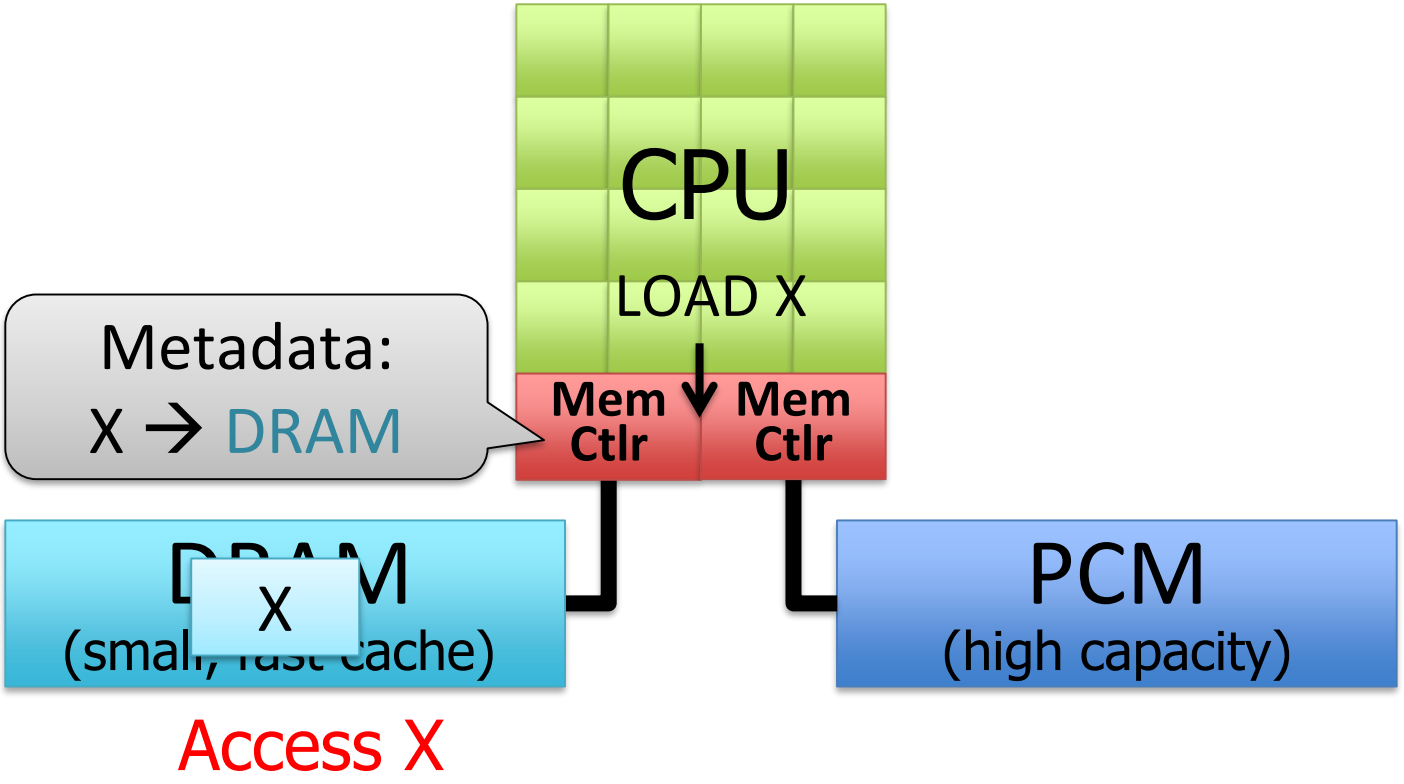
Managing Hybrid Memories

Another Challenge

Designing Effective Large (DRAM) Caches

One Problem with Large DRAM Caches

- A large DRAM cache requires a large metadata (tag + block-based information) store
- How do we design an efficient DRAM cache?



Idea 1: Tags in Memory

- Store tags in the same row as data in DRAM
  - Store metadata in same row as their data
  - Data and metadata can be accessed together

- Benefit: No on-chip tag storage overhead
- Downsides:
  - Cache hit determined only after a DRAM access
  - Cache hit requires two DRAM accesses

Idea 2: Cache Tags in SRAM

- Recall Idea 1: Store all metadata in DRAM
  - To reduce metadata storage overhead

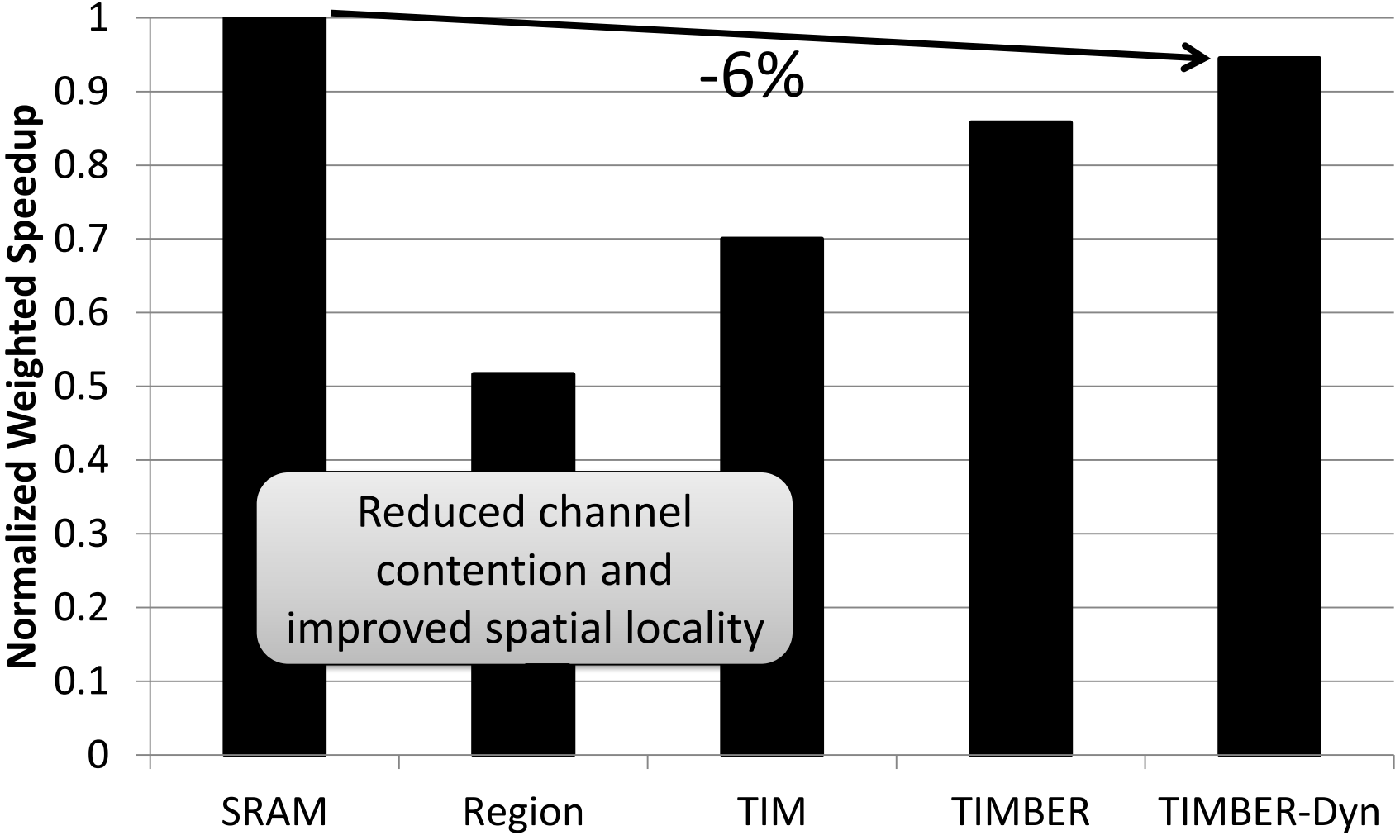
- Idea 2: Cache in on-chip SRAM frequently-accessed metadata
  - Cache only a small amount to keep SRAM size small

Idea 3: Dynamic Data Transfer Granularity

- Some applications benefit from caching more data
  - They have good spatial locality
- Others do not
  - Large granularity wastes bandwidth and reduces cache utilization

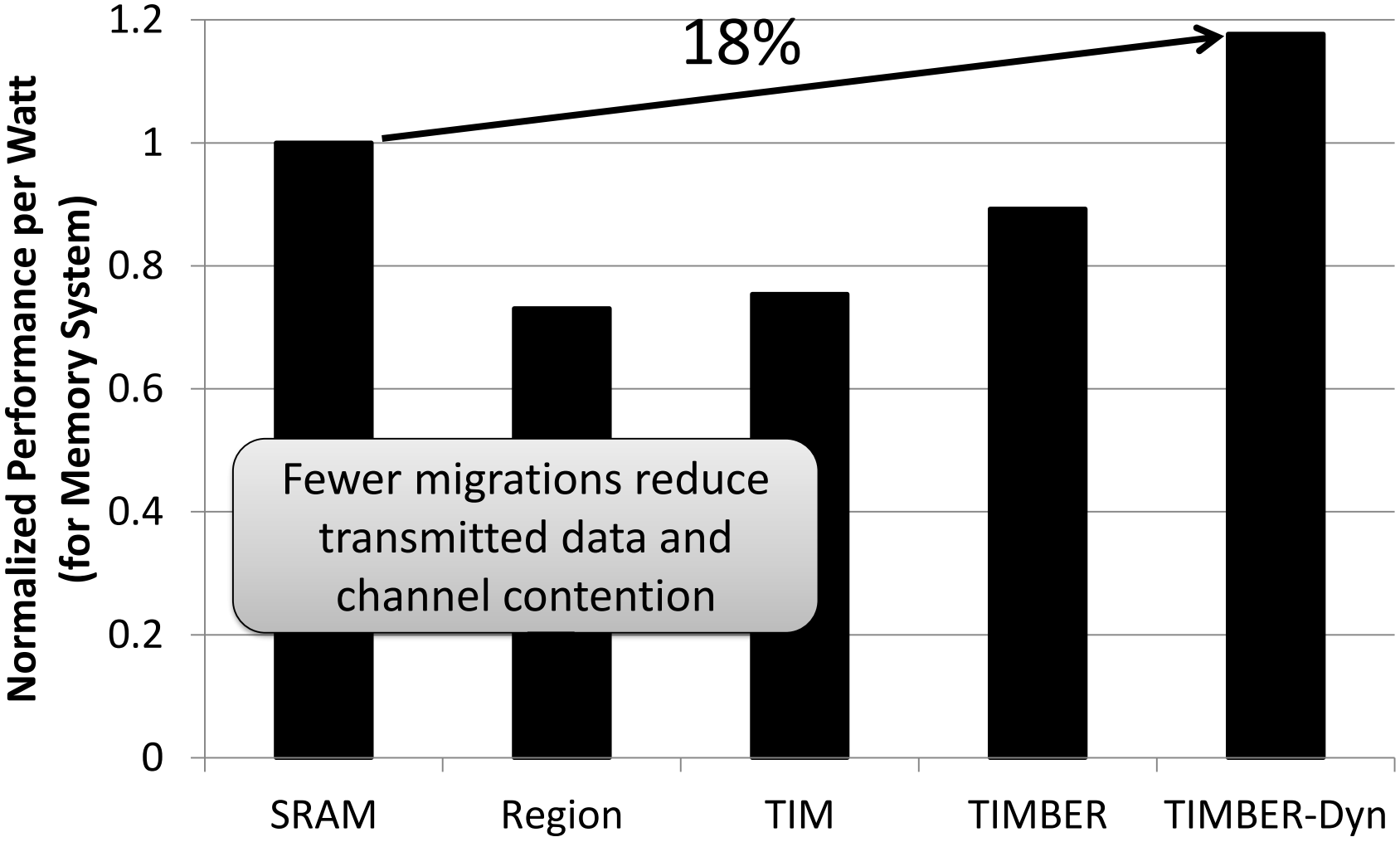
- Idea 3: Simple dynamic caching granularity policy
  - Cost-benefit analysis to determine best DRAM cache block size
  - Group main memory into sets of rows
  - Different sampled row sets follow different fixed caching granularities
  - The rest of main memory follows the best granularity
    - Cost–benefit analysis: access latency versus number of cachings
    - Performed every quantum

TIMBER Performance



Meza, Chang, Yoon, Mutlu, Ranganathan, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.

TIMBER Energy Efficiency



Meza, Chang, Yoon, Mutlu, Ranganathan, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.

On Large DRAM Cache Design

- Justin Meza, Jichuan Chang, HanBin Yoon, Onur Mutlu, and Parthasarathy Ranganathan,
  "Enabling Efficient and Scalable Hybrid Memories Using Fine-Granularity DRAM Cache Management"
  IEEE Computer Architecture Letters (***CAL***), February 2012.

Enabling Efficient and Scalable Hybrid Memories Using Fine-Granularity DRAM Cache Management

Justin Meza* Jichuan Chang† HanBin Yoon* Onur Mutlu* Parthasarathy Ranganathan†
*Carnegie Mellon University †Hewlett-Packard Labs
{meza,hanbinyoon,onur}@cmu.edu {jichuan.chang,partha.ranganathan}@hp.com

DRAM Caches: Many Recent Options

Table 1: Summary of Operational Characteristics of Different State-of-the-Art DRAM Cache Designs – We assume perfect way prediction for Unison Cache. Latency is relative to the access time of the off-package DRAM (see Section 6 for baseline latencies). We use different colors to indicate the high (dark red), medium (white), and low (light green) overhead of a characteristic.

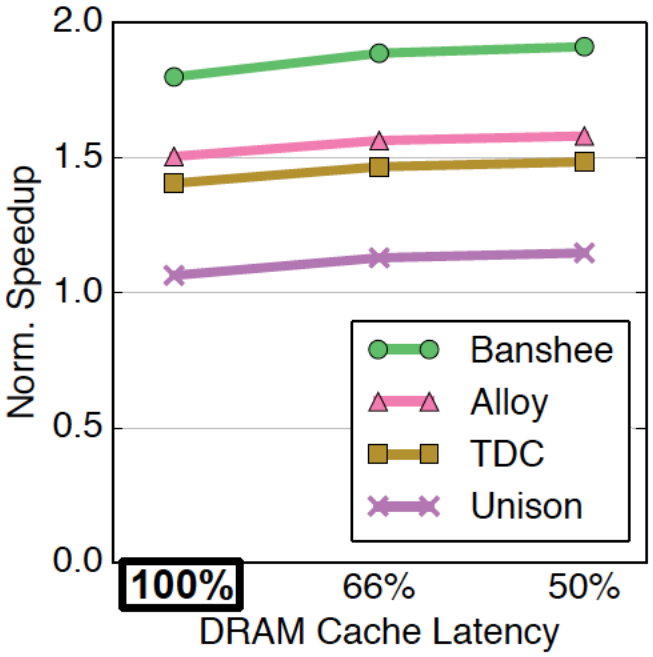
Scheme	DRAM Cache Hit	DRAM Cache Miss	Replacement Traffic	Replacement Decision	Large Page Caching
Unison [32]	In-package traffic: 128 B (data + tag read and update) Latency: ~1x	In-package traffic: 96 B (spec. data + tag read) Latency: ~2x	On every miss Footprint size [31]	Hardware managed, set-associative, LRU	Yes
Alloy [50]	In-package traffic: 96 B (data + tag read) Latency: ~1x	In-package traffic: 96 B (spec. data + tag read) Latency: ~2x	On some misses Cacheline size (64 B)	Hardware managed, direct-mapped, stochastic [20]	Yes
TDC [38]	In-package traffic: 64 B Latency: ~1x TLB coherence	In-package traffic: 0 B Latency: ~1x TLB coherence	On every miss Footprint size [28]	Hardware managed, fully-associative, FIFO	No
HMA [44]	In-package traffic: 64 B Latency: ~1x	In-package traffic: 0 B Latency: ~1x	Software managed, high replacement cost		Yes
Banshee (This work)	In-package traffic: 64 B Latency: ~1x	In-package traffic: 0 B Latency: ~1x	Only for hot pages Page size (4 KB)	Hardware managed, set-associative, frequency based	Yes

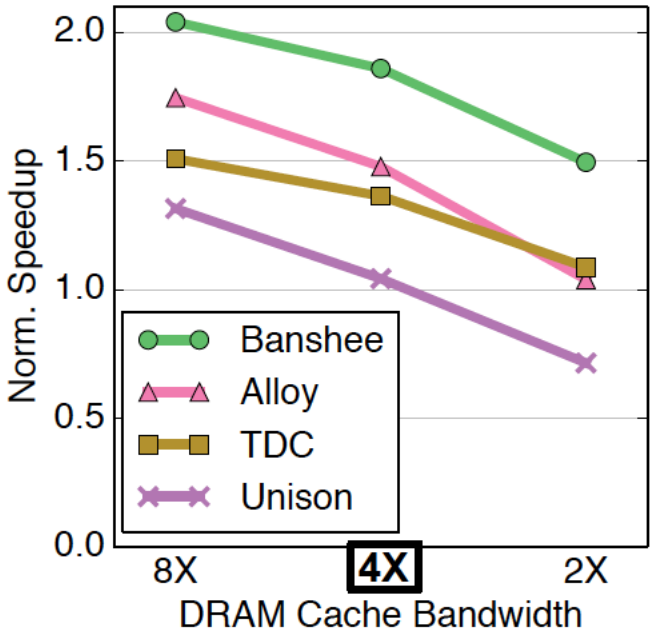
Yu+, "Banshee: Bandwidth-Efficient DRAM Caching via Software/Hardware Cooperation," MICRO 2017.

Banshee [MICRO 2017]

- Tracks presence in cache using TLB and Page Table
  - No tag store needed for DRAM cache
  - Enabled by a new lightweight lazy TLB coherence protocol

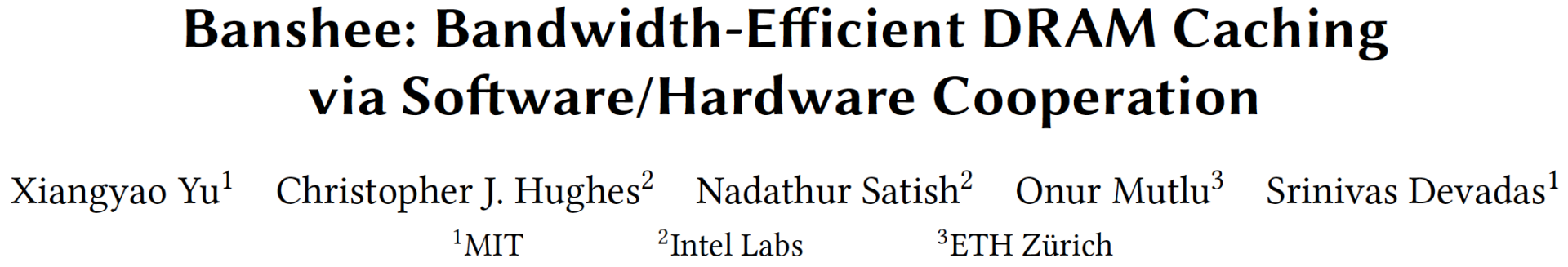
- New bandwidth-aware frequency-based replacement policy





More on Banshee

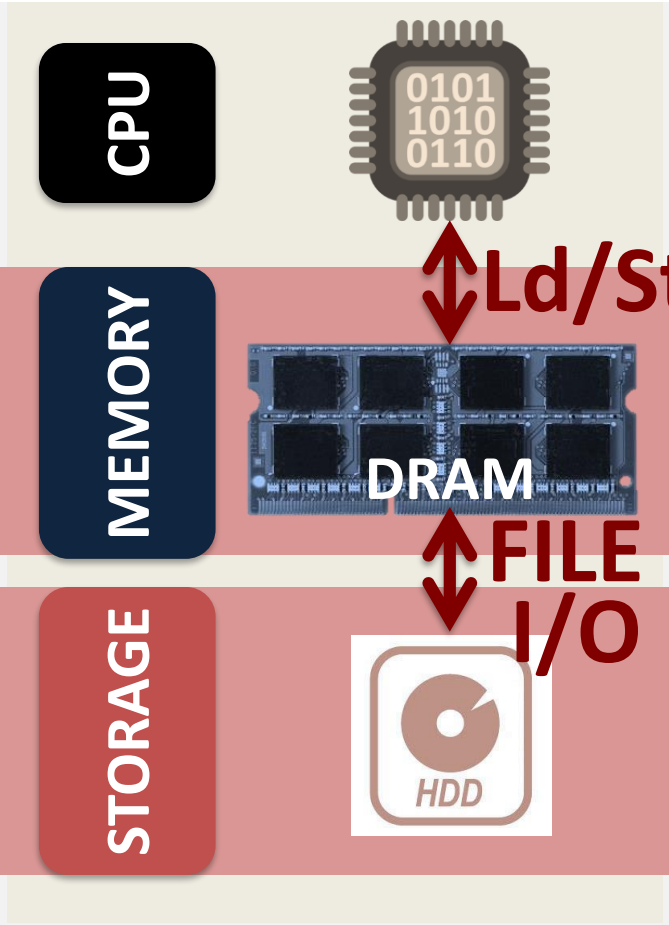
- Xiangyao Yu, Christopher J. Hughes, Nadathur Satish, Onur Mutlu, and Srinivas Devadas,
  "Banshee: Bandwidth-Efficient DRAM Caching via Software/Hardware Cooperation"
  *Proceedings of the 50th International Symposium on Microarchitecture (**MICRO**)*, Boston, MA, USA, October 2017.



Other Opportunities with Emerging Technologies

- Merging of memory and storage
  - e.g., a single interface to manage all data
- New applications
  - e.g., ultra-fast checkpoint and restore
- More robust system design
  - e.g., reducing data loss
- Processing tightly-coupled with memory
  - e.g., enabling efficient search and filtering

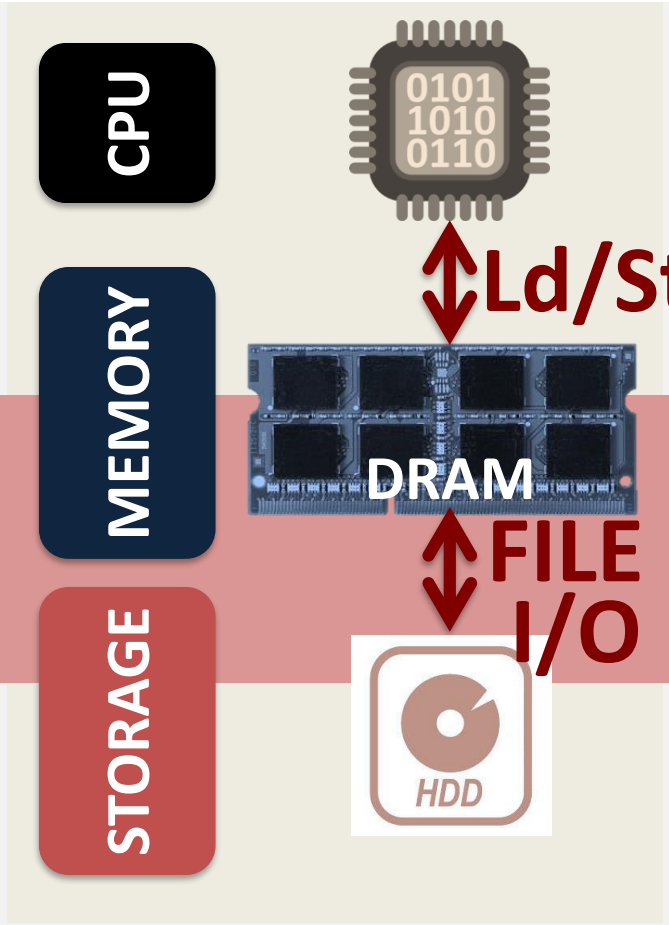
TWO-LEVEL STORAGE MODEL



VOLATILE
FAST
BYTE ADDR

NONVOLATILE
SLOW
BLOCK ADDR

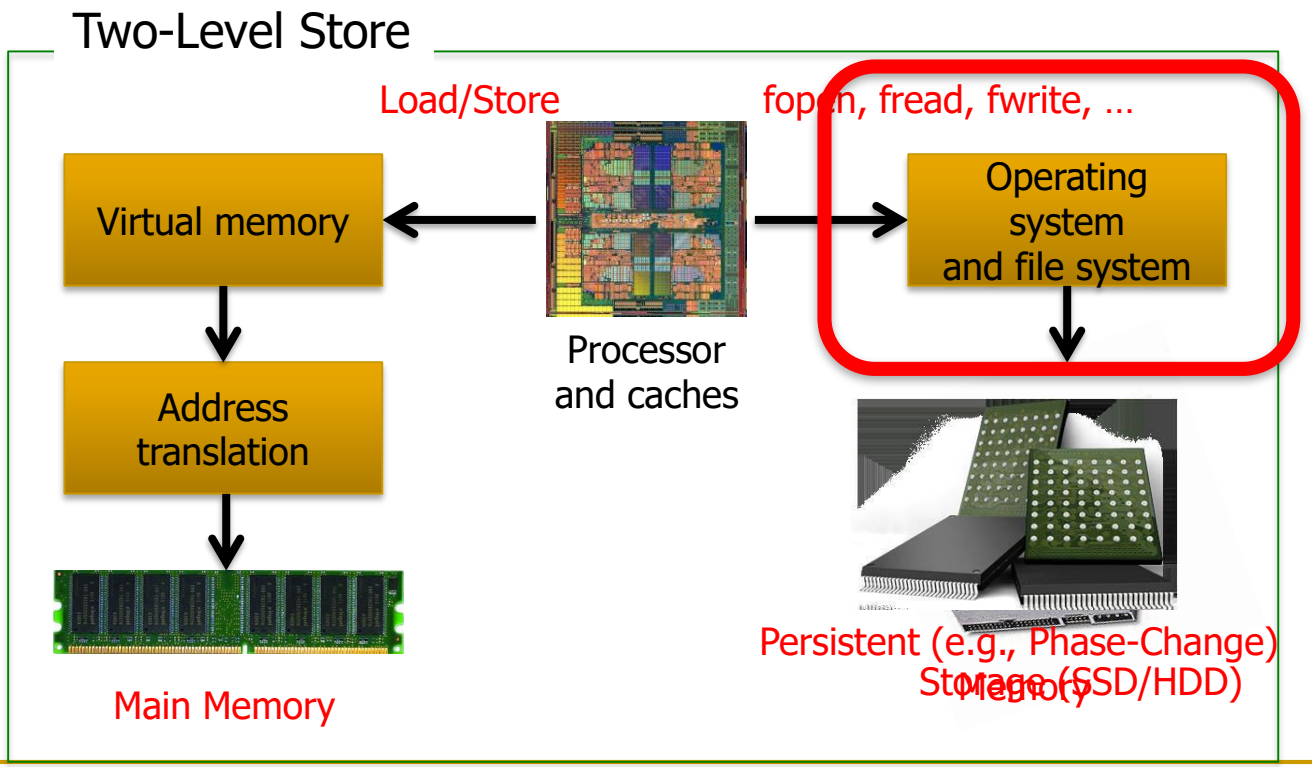
TWO-LEVEL STORAGE MODEL



Non-volatile memories combine characteristics of memory and storage

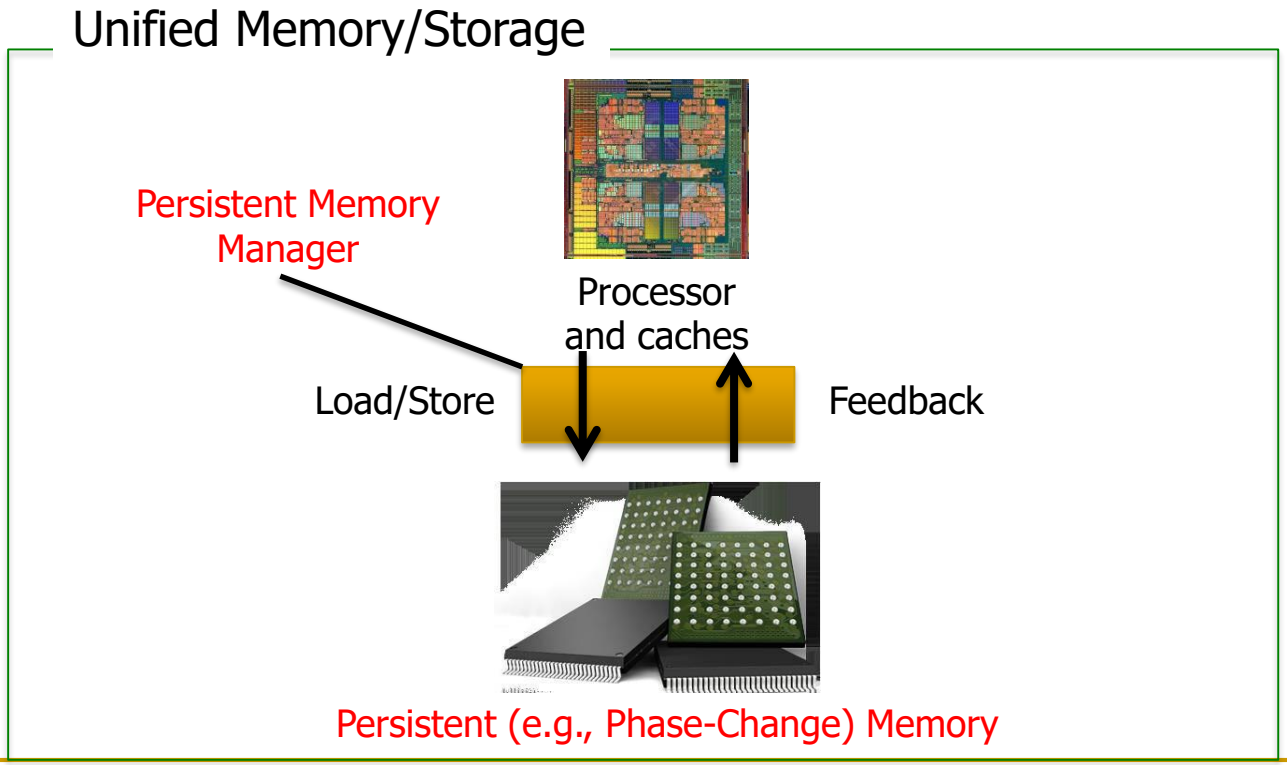
Two-Level Memory/Storage Model

- The traditional two-level storage model is a bottleneck with NVM
  - **Volatile** data in memory → a **load/store** interface
  - **Persistent** data in storage → a **file system** interface
  - Problem: Operating system (OS) and file system (FS) code to locate, translate, buffer data become performance and energy bottlenecks with fast NVM stores



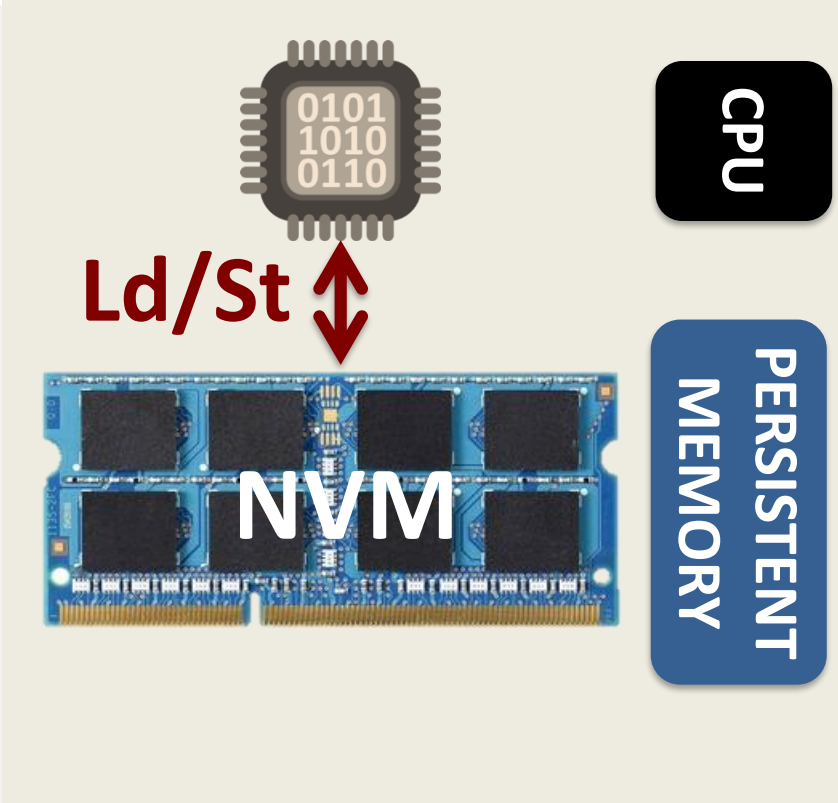
Unified Memory and Storage with NVM

- Goal: Unify memory and storage management in a single unit to eliminate wasted work to locate, transfer, and translate data
  - Improves both energy and performance
  - Simplifies programming model as well



Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.

PERSISTENT MEMORY

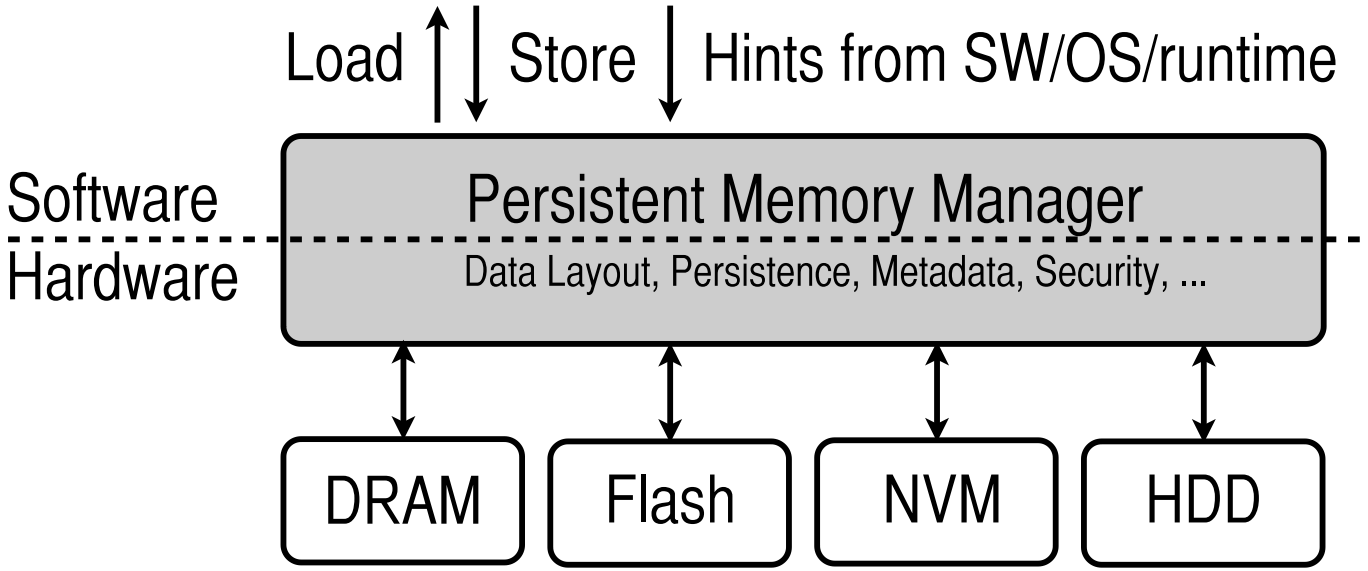


Provides an opportunity to manipulate persistent data directly

The Persistent Memory Manager (PMM)

```
1  int main(void) {
2    // data in file.dat is persistent
3    FILE myData = "file.dat";
4    myData = new int[64];
5  }
6  void updateValue(int n, int value) {
7    FILE myData = "file.dat";
8    myData[n] = value; // value is persistent
9  }
```

Persistent objects



PMM uses access and hint information to allocate, locate, migrate and access data in the heterogeneous array of devices

The Persistent Memory Manager (PMM)

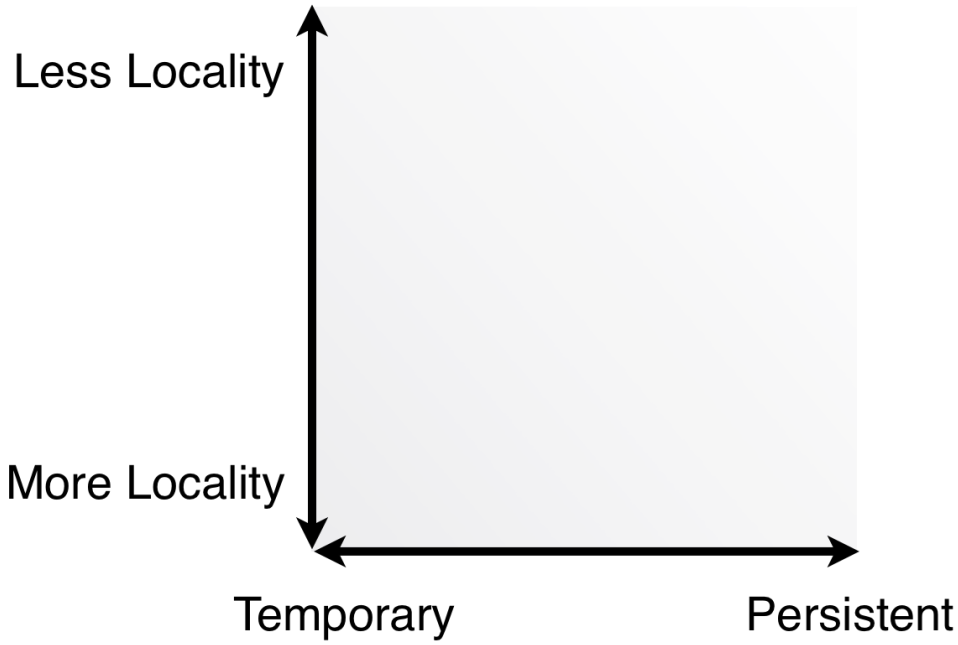
- Exposes a load/store interface to access persistent data
  - Applications can directly access persistent memory → no conversion, translation, location overhead for persistent data
- Manages data placement, location, persistence, security
  - To get the best of multiple forms of storage
- Manages metadata storage and retrieval
  - This can lead to overheads that need to be managed
- Exposes hooks and interfaces for system software
  - To enable better data placement and management decisions
- Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.

Efficient Data Mapping among Heterogeneous Devices

- A persistent memory exposes a large, persistent address space
  - But it may use many different devices to satisfy this goal
  - From fast, low-capacity volatile DRAM to slow, high-capacity non-volatile HDD or Flash
  - And other NVM devices in between

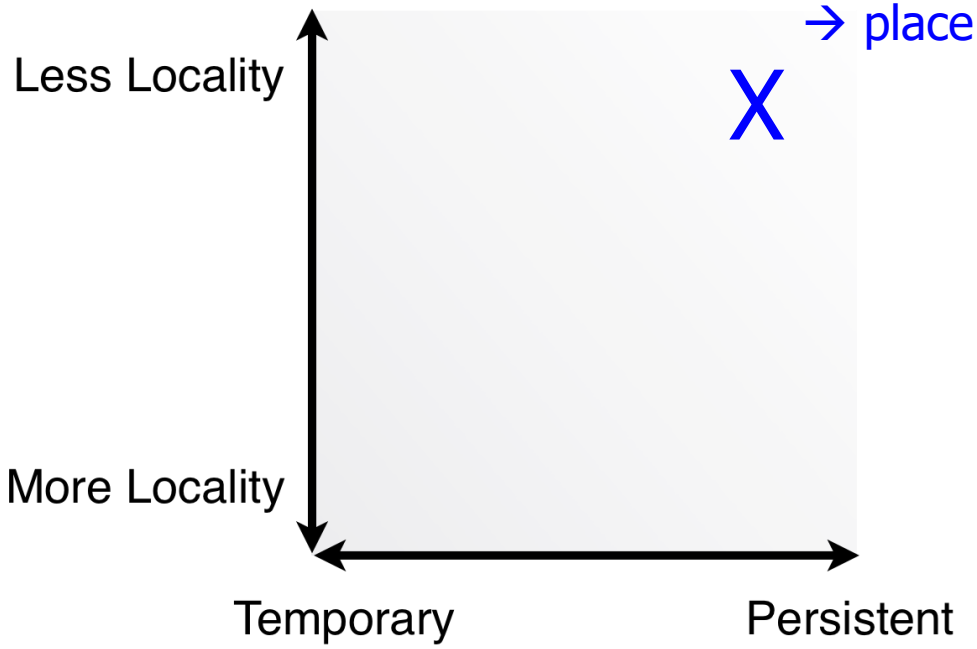
- Performance and energy can benefit from good placement of data among these devices
  - Utilizing the strengths of each device and avoiding their weaknesses, if possible
  - For example, consider two important application characteristics: locality and persistence

Efficient Data Mapping among Heterogeneous Devices

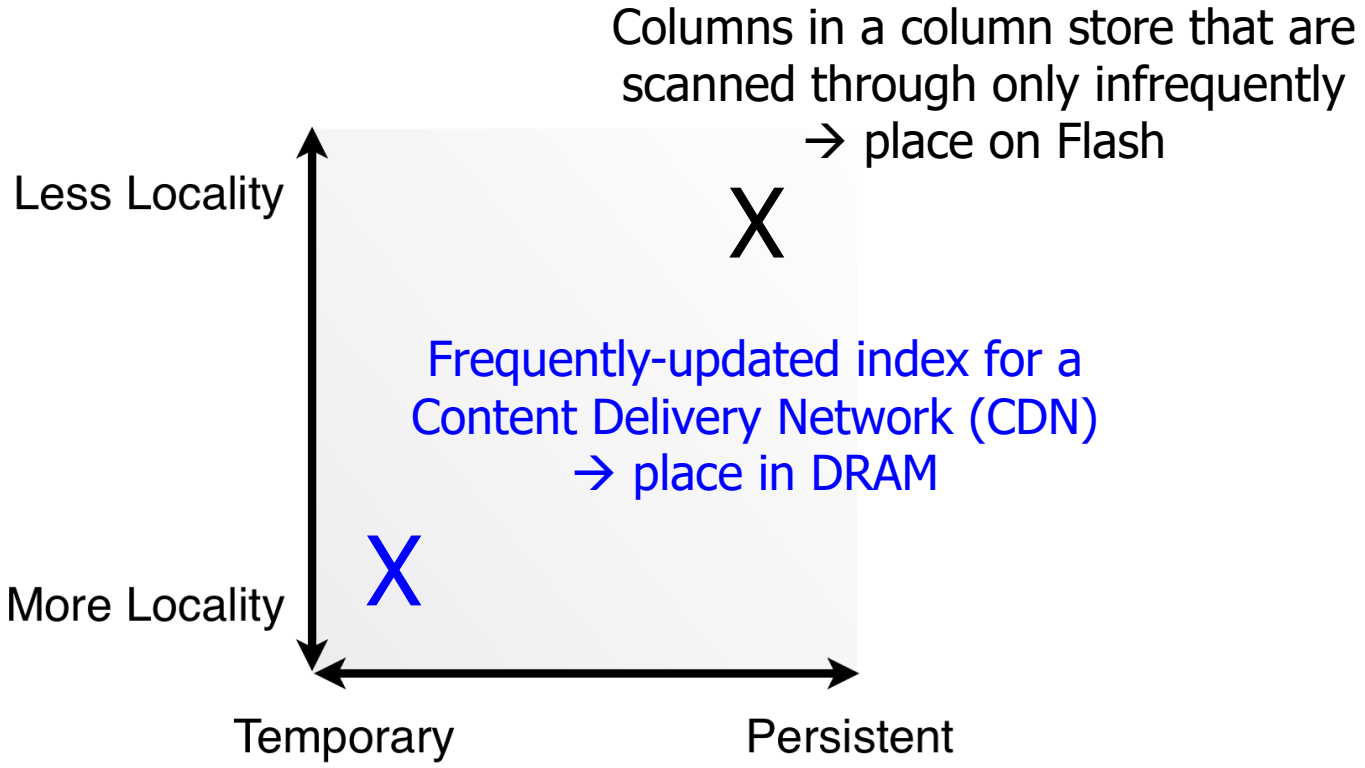


Efficient Data Mapping among Heterogeneous Devices

Columns in a column store that are scanned through only infrequently → place on Flash



Efficient Data Mapping among Heterogeneous Devices

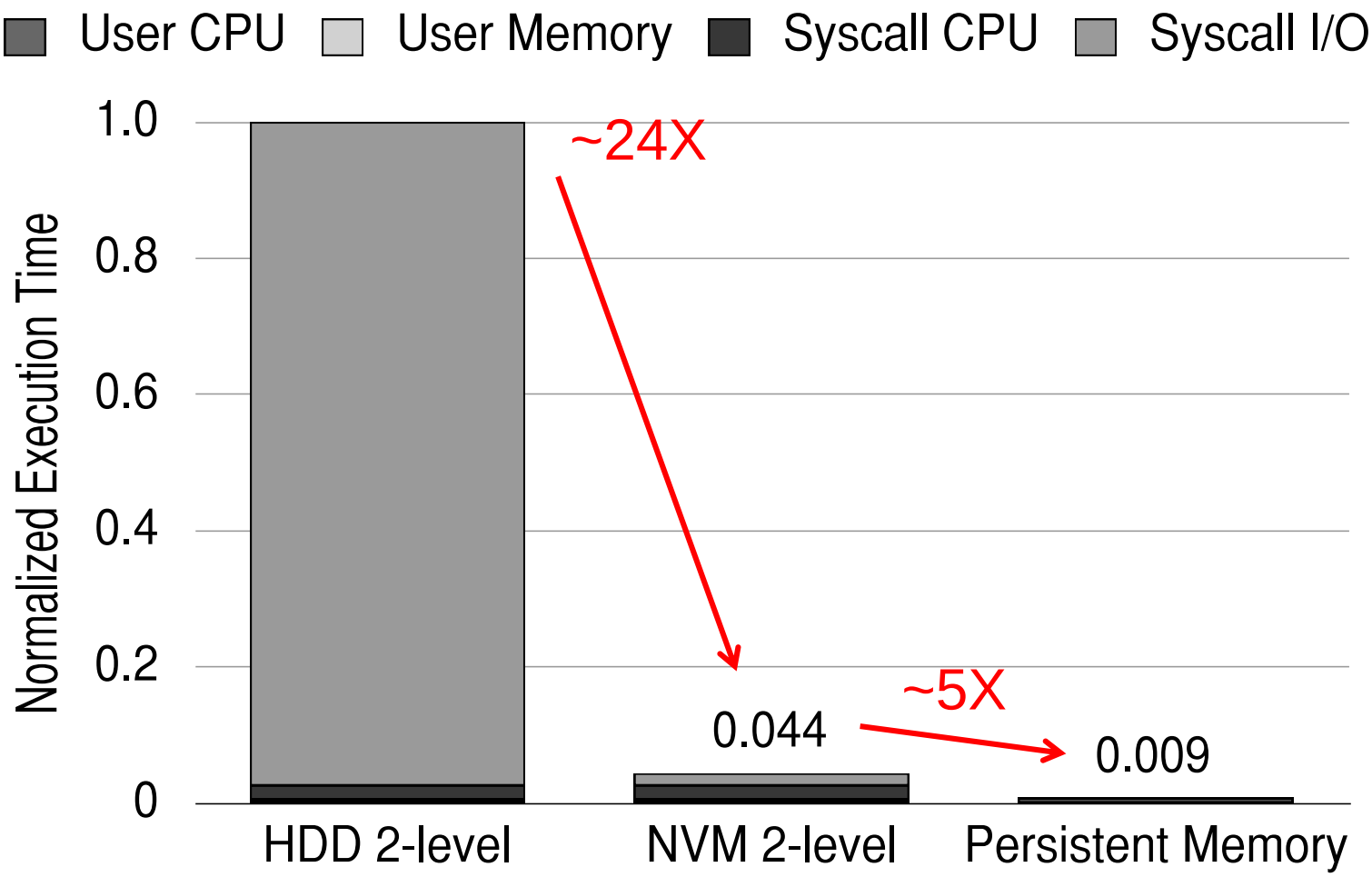


Applications or system software can provide hints for data placement

Evaluated Systems

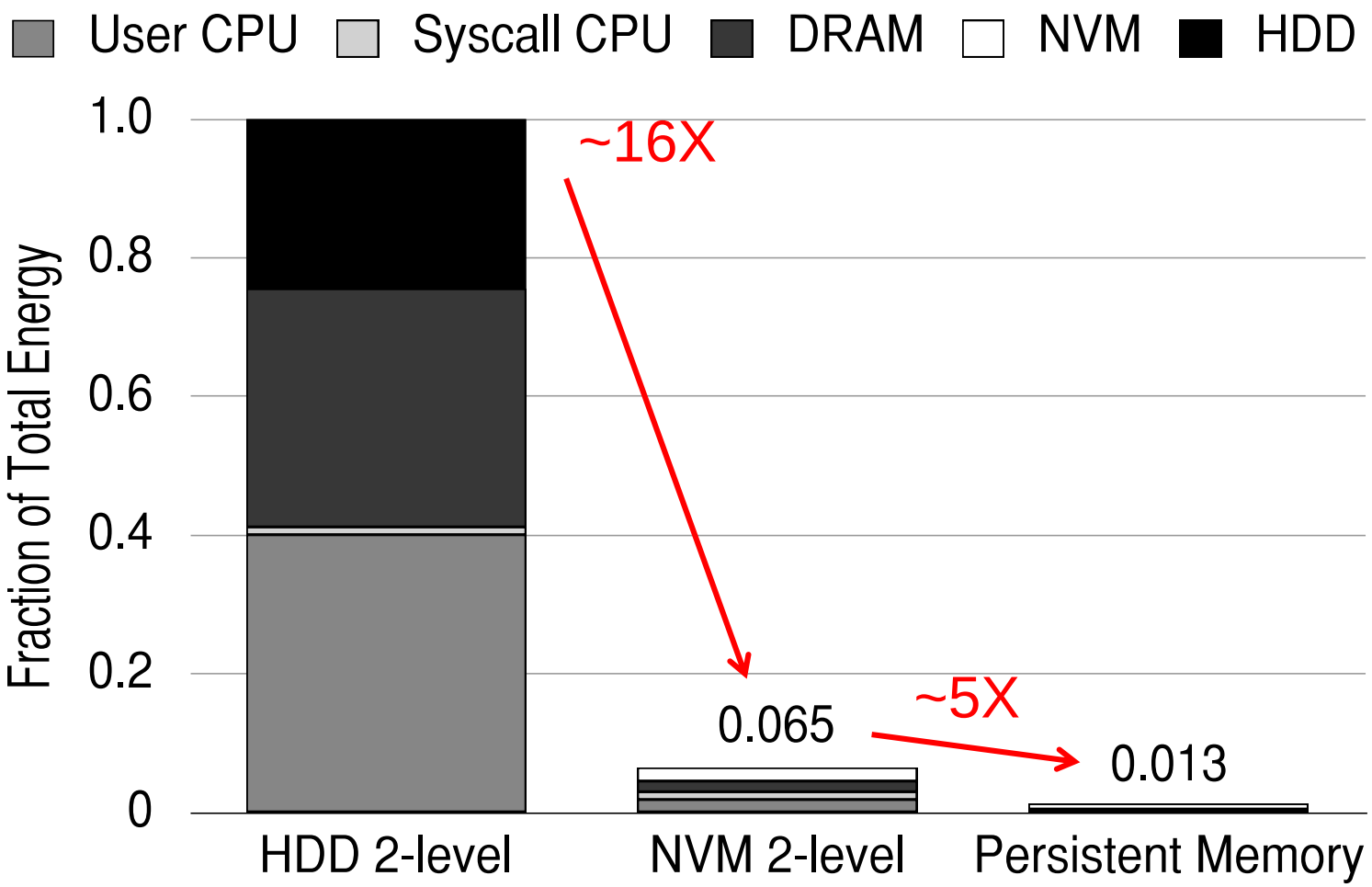
- HDD Baseline
  - Traditional system with volatile DRAM memory and persistent HDD storage
  - Overheads of operating system and file system code and buffering
- NVM Baseline (NB)
  - Same as HDD Baseline, but HDD is replaced with NVM
  - Still has OS/FS overheads of the two-level storage model
- Persistent Memory (PM)
  - Uses only NVM (no DRAM) to ensure full-system persistence
  - All data accessed using loads and stores
  - Does not waste time on system calls
  - Data is manipulated directly on the NVM device

Performance Benefits of a Single-Level Store



Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.

Energy Benefits of a Single-Level Store



Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.

On Persistent Memory Benefits & Challenges

- Justin Meza, Yixin Luo, Samira Khan, Jishen Zhao, Yuan Xie, and Onur Mutlu,
  "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory"
  *Proceedings of the 5th Workshop on Energy-Efficient Design (**WEED**)*, Tel-Aviv, Israel, June 2013. Slides (pptx) Slides (pdf)

A Case for Efficient Hardware/Software Cooperative Management of Storage and Memory

Justin Meza* Yixin Luo* Samira Khan*‡ Jishen Zhao† Yuan Xie†§ Onur Mutlu*
*Carnegie Mellon University †Pennsylvania State University ‡Intel Labs §AMD Research

Challenge and Opportunity

Combined
Memory & Storage

Challenge and Opportunity

A Unified Interface to
All Data

Computer Architecture

Lecture 13: Emerging Memory Technologies

Prof. Onur Mutlu
ETH Zürich

Fall 2018

31 October 2018

One Key Challenge in Persistent Memory

- How to ensure consistency of system/data if all memory is persistent?

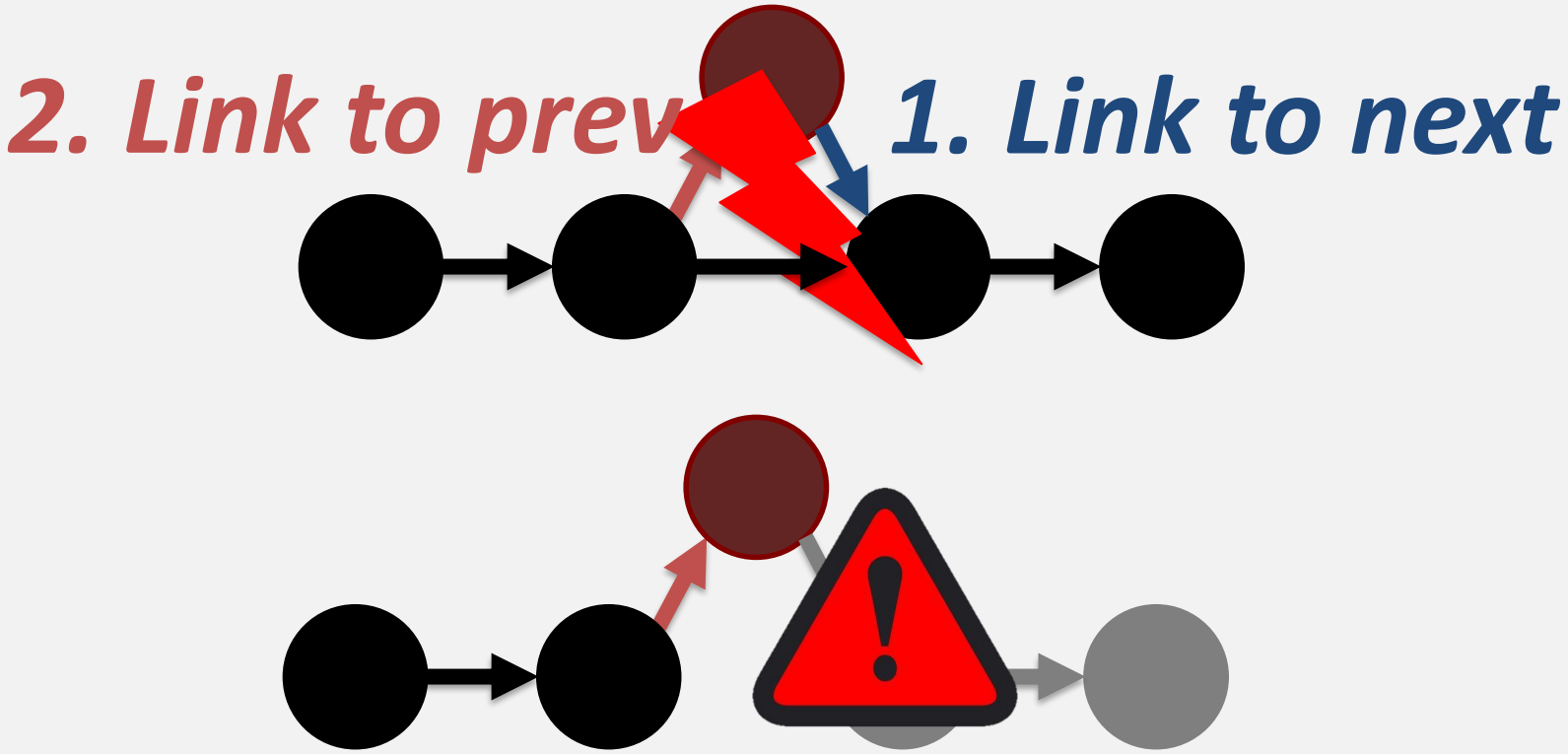
- Two extremes
  - Programmer transparent: Let the system handle it
  - Programmer only: Let the programmer handle it

- Many alternatives in-between…

We did not cover the remaining slides in lecture.

CRASH CONSISTENCY PROBLEM

Add a node to a linked list



System crash can result in inconsistent memory state

CURRENT SOLUTIONS

Explicit interfaces to manage consistency

– **NV-Heaps** [ASPLOS'11], **BPFS** [SOSP'09], **Mnemosyne** [ASPLOS'11]

```
AtomicBegin {
        Insert a new node;
} AtomicEnd;
```

Limits adoption of NVM

Have to rewrite code with clear partition between volatile and non-volatile data

Burden on the programmers

CURRENT SOLUTIONS

Explicit interfaces to manage consistency

- **NV-Heaps** [ASPLOS'11], **BPFS** [SOSP'09], **Mnemosyne** [ASPLOS'11]

Example Code

update a node in a persistent hash table

```
void hashtable_update(hashtable_t* ht,
                      void *key, void *data)
{
    list_t* chain = get_chain(ht, key);
    pair_t* pair;
    pair_t updatePair;
    updatePair.first = key;
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CURRENT SOLUTIONS

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void TMhashtable_update(TMARCGDECL
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```

CURRENT SOLUTIONS

Manual declaration of persistent components

```
void TMhashtable_update(TMARCGDECL
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Need a new implementation

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Need a new implementation

Third party code can be inconsistent

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  pair->second = data;
}
```

Need a new implementation

Prohibited Operation `=` **Third party code can be inconsistent**

Burden on the programmers

OUR APPROACH: ThyNVM

Goal:
Software transparent consistency in persistent memory systems

Key Idea:
Periodically checkpoint state; recover to previous checkpt on crash

ThyNVM: Summary

A new hardware-based checkpointing mechanism

- **Checkpoints** at *multiple granularities* to reduce both checkpointing latency and metadata overhead
- **Overlaps** *checkpointing* and *execution to* reduce checkpointing latency
- **Adapts** to *DRAM and NVM* characteristics

Performs within 4.9% of an *idealized DRAM* with zero cost consistency

OUTLINE

Crash Consistency Problem

Current Solutions

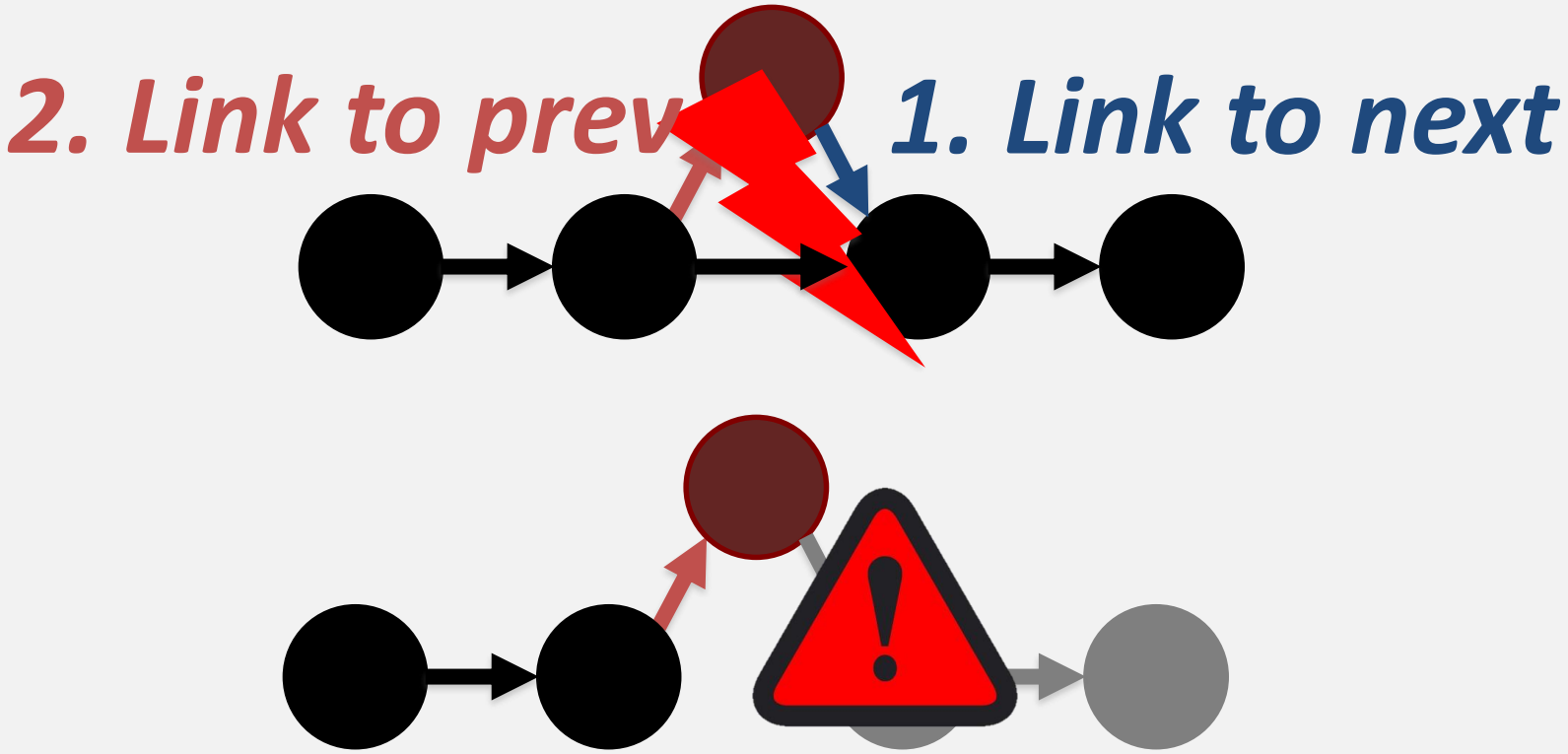
ThyNVM

Evaluation

Conclusion

CRASH CONSISTENCY PROBLEM

Add a node to a linked list



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OUTLINE

Crash Consistency Problem

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Need a new implementation

CURRENT SOLUTIONS

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Third party code can be inconsistent

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Manual declaration of persistent components

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}
```

Need a new implementation

Prohibited Operation `=` **Third party code can be inconsistent**

Burden on the programmers

OUTLINE

Crash Consistency Problem

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ThyNVM

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OUR GOAL

Software transparent consistency in persistent memory systems

- **Execute** *legacy applications*
- **Reduce burden** *on programmers*
- **Enable** *easier integration of NVM*

NO MODIFICATION IN THE CODE

```
void hashtable_update(hashtable_t* ht,
                      void *key, void *data)
{
list_t* chain = get_chain(ht, key);
pair_t* pair;
pair_t updatePair;
updatePair.first = key;
pair = (pair_t*) list_find(chain,
                                    &updatePair);
pair->second = data;
}
```

RUN THE EXACT SAME CODE…

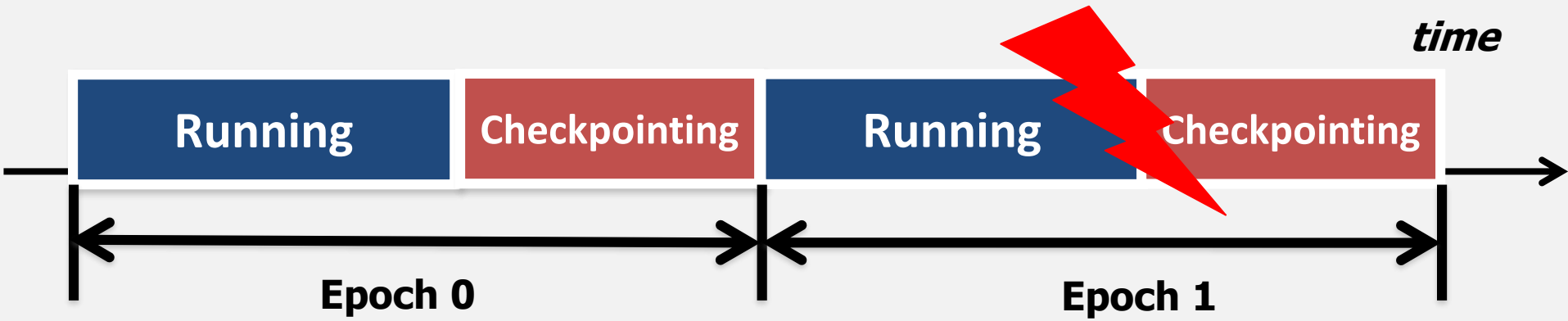
Persistent Memory System

```
void hashtable_update(hashtable_t* ht,
                      void *key, void *data){
  list_t* chain = get_chain(ht, key);
  pair_t* pair;
  pair_t updatePair;
  updatePair.first = key;
  pair = (pair_t*) list_find(chain,
                             &updatePair);
  pair->second = data;
}
```

Software transparent memory crash consistency

ThyNVM APPROACH

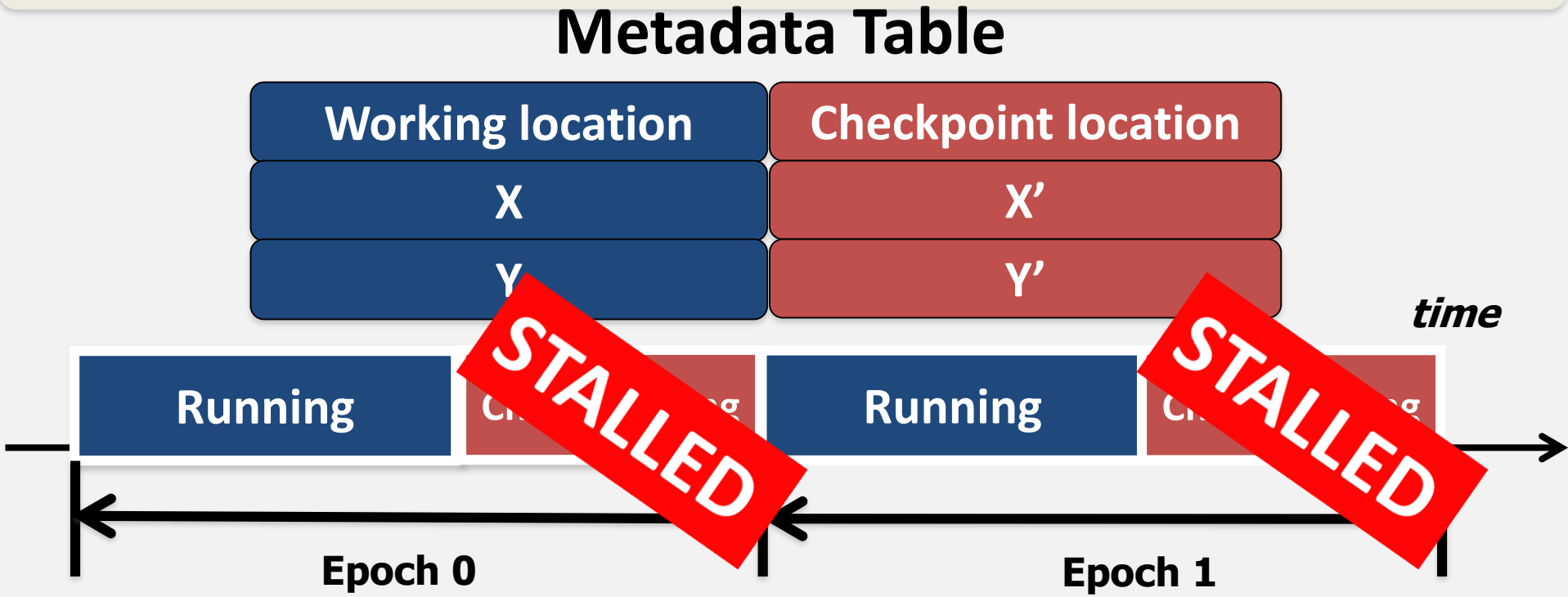
Periodic checkpointing of data managed by hardware



Transparent to application and system

CHECKPOINTING OVERHEAD

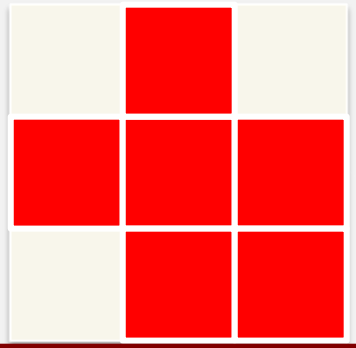
1. Metadata overhead



2. Checkpointing latency

1. METADATA AND CHECKPOINTING GRANULARITY

Working location	Checkpoint location
X	X’
Y	Y’



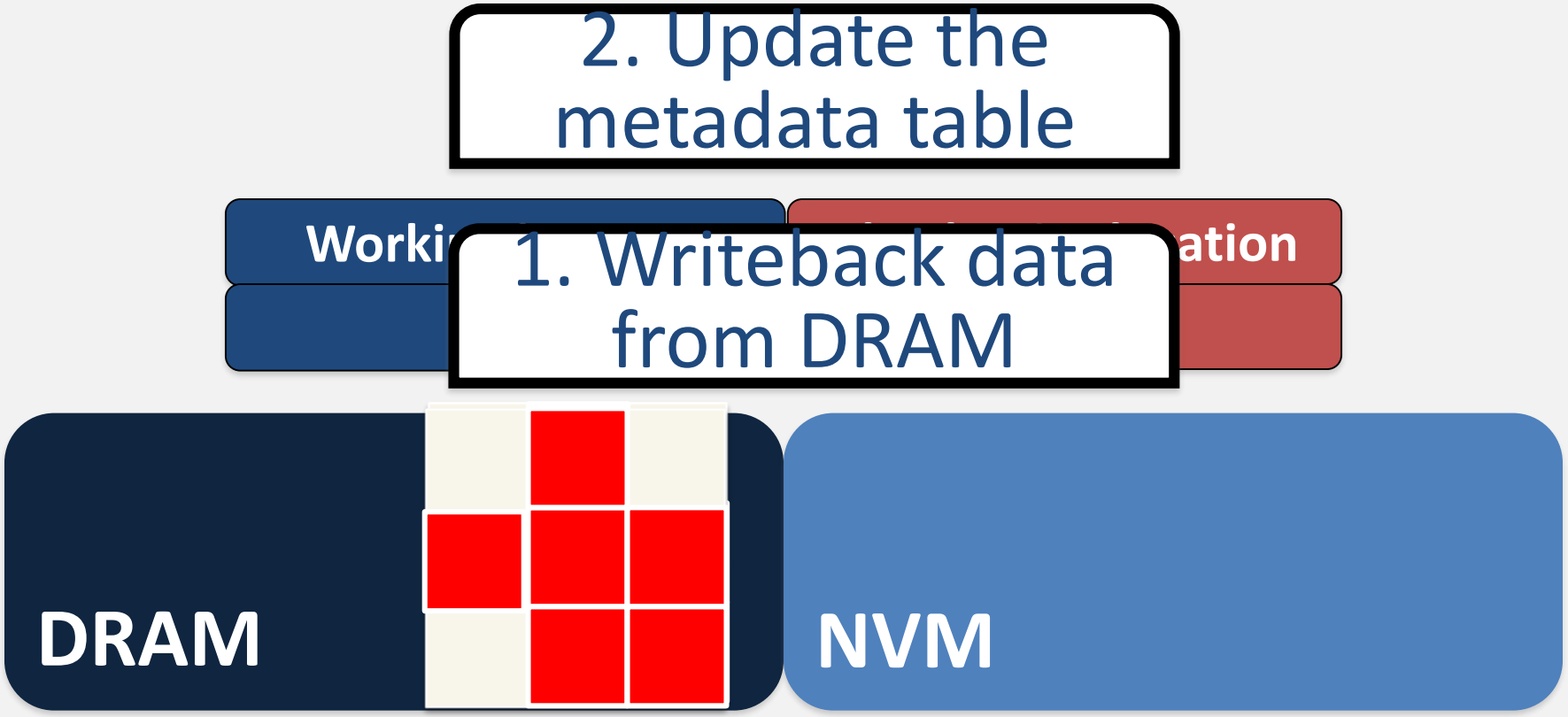
PAGE

CACHE BLOCK

PAGE GRANULARITY	BLOCK GRANULARITY
One Entry Per Page Small Metadata	One Entry Per Block Huge Metadata

2. LATENCY AND LOCATION

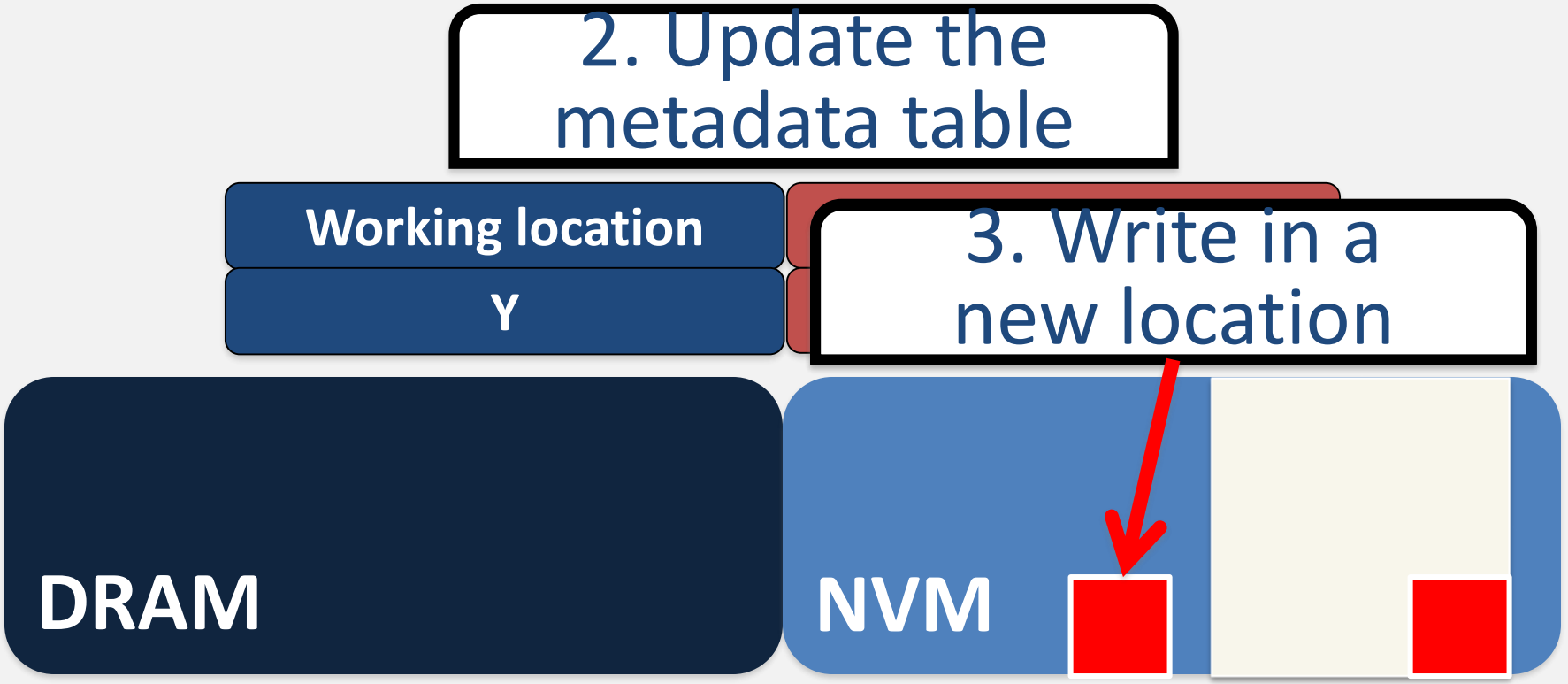
DRAM-BASED WRITEBACK



Long latency of writing back data to NVM

2. LATENCY AND LOCATION

NVM-BASED REMAPPING



Short latency in NVM-based remapping

ThyNVM KEY MECHANISMS

Checkpointing granularity

- *Small granularity: large metadata*
- *Large granularity: small metadata*

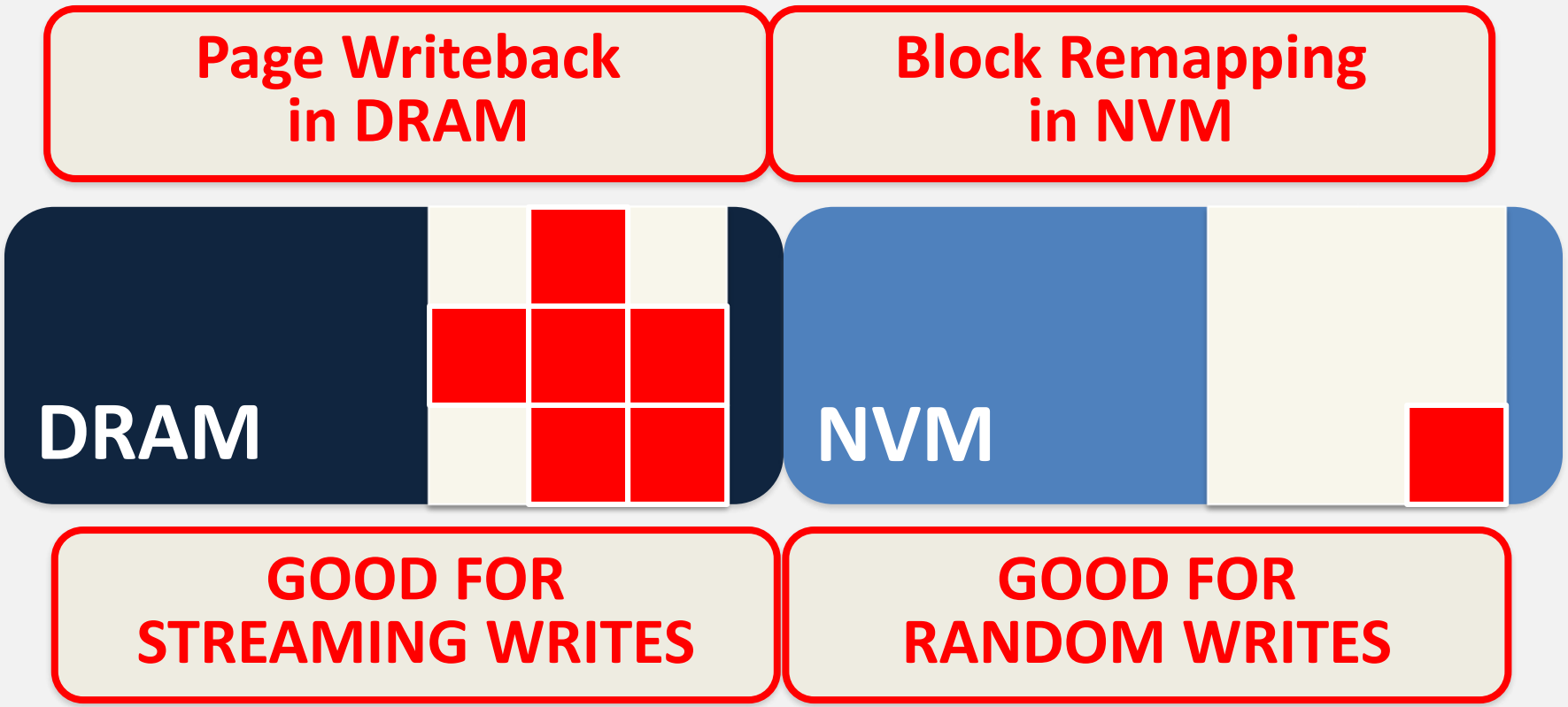
Latency and location

- *Writeback from DRAM: long latency*
- *Remap in NVM: short latency*

Based on these, we propose two key mechanisms

1. Dual granularity checkpointing
2. Overlap of execution and checkpointing

1. DUAL GRANULARITY CHECKPOINTING



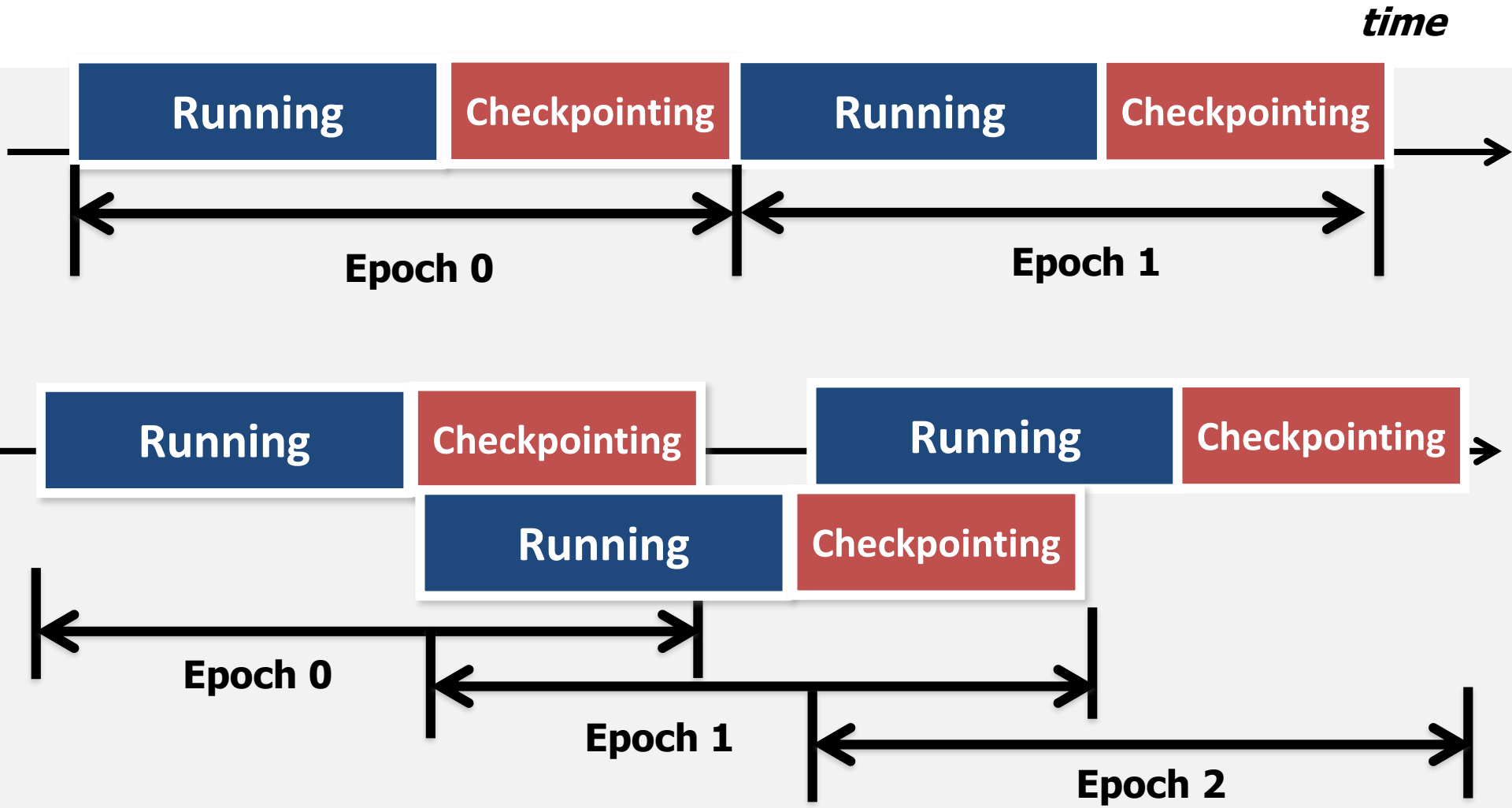
High write locality pages in DRAM, low write locality pages in NVM

TRADEOFF SPACE

		Checkpointing granularity	
		Small (cache block)	Large (page)
Location of working copy	DRAM (based on writeback)	❶ *Inefficient* ✘ **Large metadata overhead** ✘ **Long checkpointing latency**	❷ *Partially efficient* ✔ **Small metadata overhead** ✘ Long checkpointing latency
	NVM (based on remapping)	❸ *Partially efficient* ✘ Large metadata overhead ✔ **Short checkpointing latency** ✔ Fast remapping	❹ *Inefficient* ✔ Small metadata overhead ✔ Short checkpointing latency ✘ **Slow remapping** (on the critical path)

Table 1: Tradeoff space of options combining checkpointing granularity choice and location choice of the working copy of data. The table shows four options and their pros and cons. Boldfaced text indicates the most critical pro or con that determines the efficiency of an option.

2. OVERLAPPING CHECKPOINTING AND EXECUTION



Hides the long latency of Page Writeback

OUTLINE

Flash Memory SUMMIT

- Crash Consistency Problem
- Current Solutions
- ThyNVM
- **Evaluation**
- Conclusion

SYSTEM ARCHITECTURE

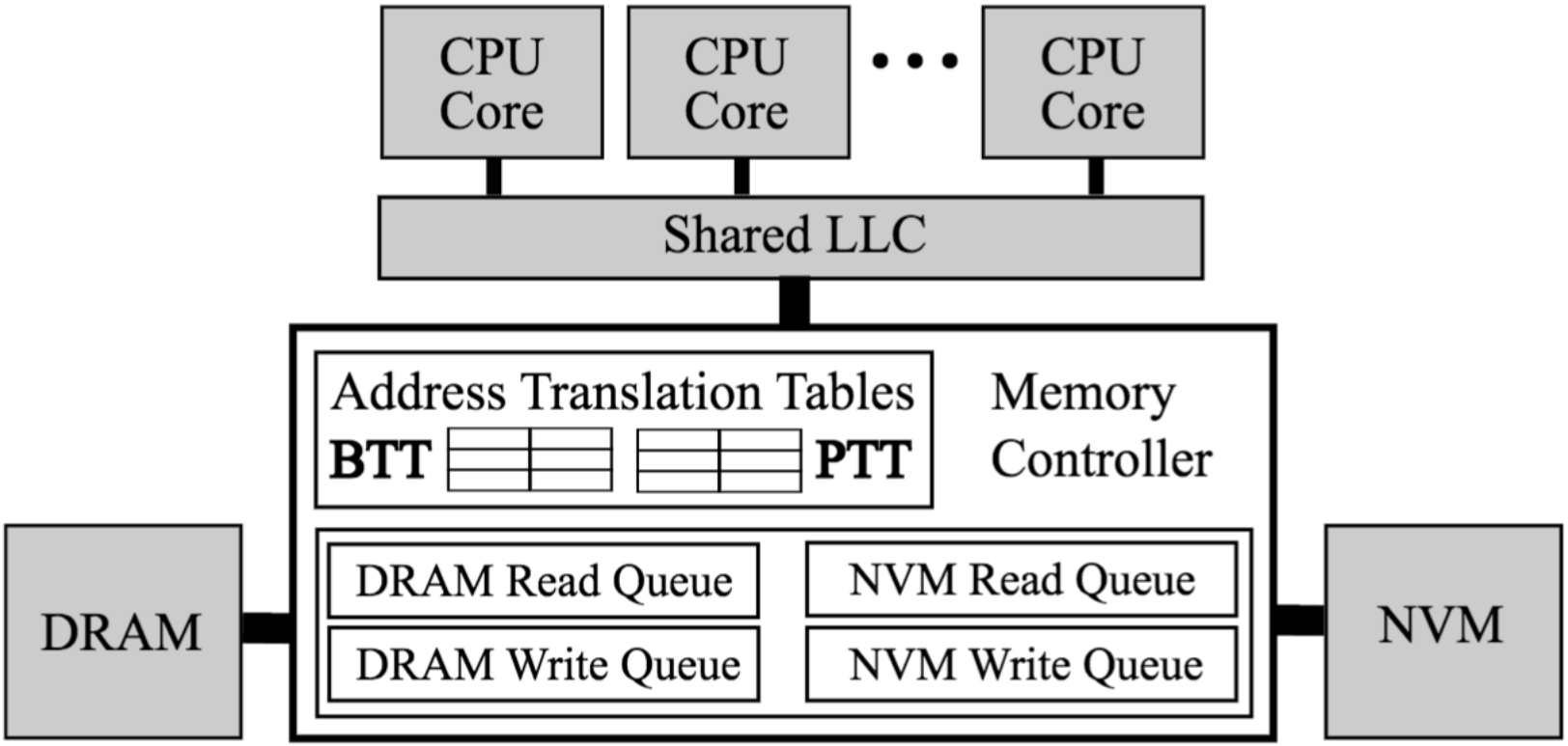
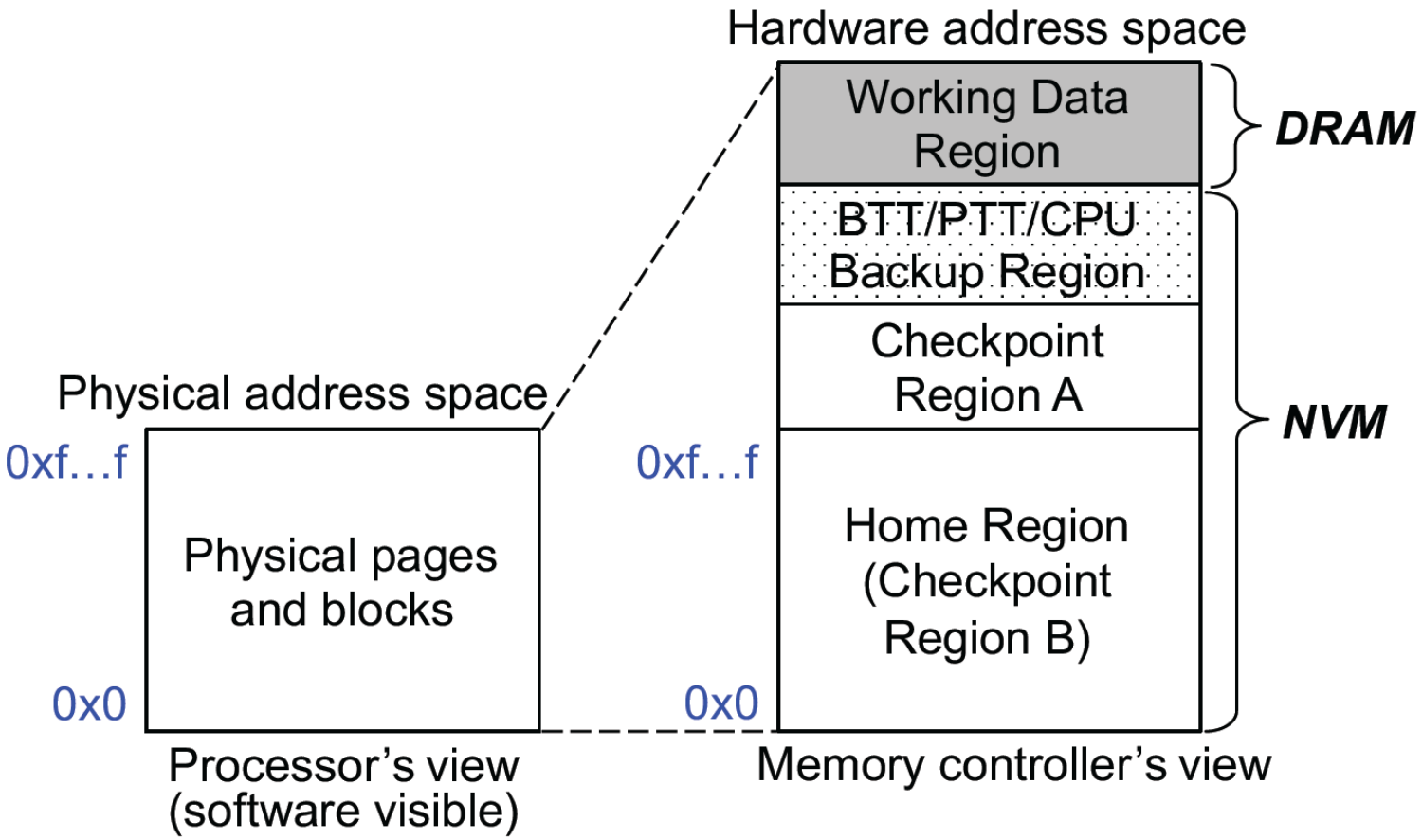


Figure 2: Architecture overview of ThyNVM.

MEMORY ADDRESS SPACE



Working Data Region: W_{active}^{page}, W_{active}^{block} (when creating C_{last})

Ckpt Regions A and B: C_{last}, C_{penult}, W_{active}^{block}

Figure 4: ThyNVM address space layout.

METHODOLOGY

Cycle accurate x86 simulator Gem5

Comparison Points:

Ideal DRAM: DRAM-based, no cost for consistency
- Lowest latency system

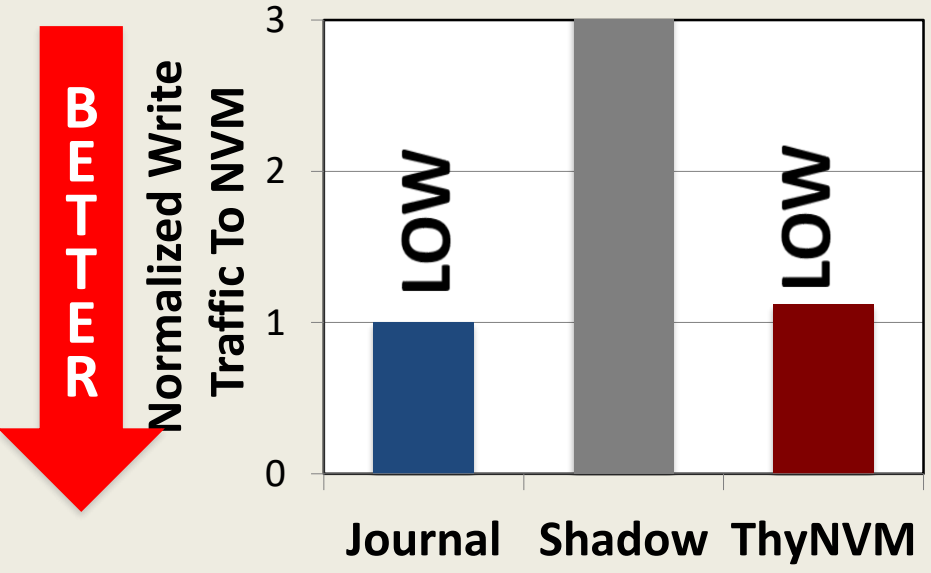
Ideal NVM: NVM-based, no cost for consistency
- NVM has higher latency than DRAM

Journaling: Hybrid, commit dirty cache blocks
- Leverages DRAM to buffer dirty blocks

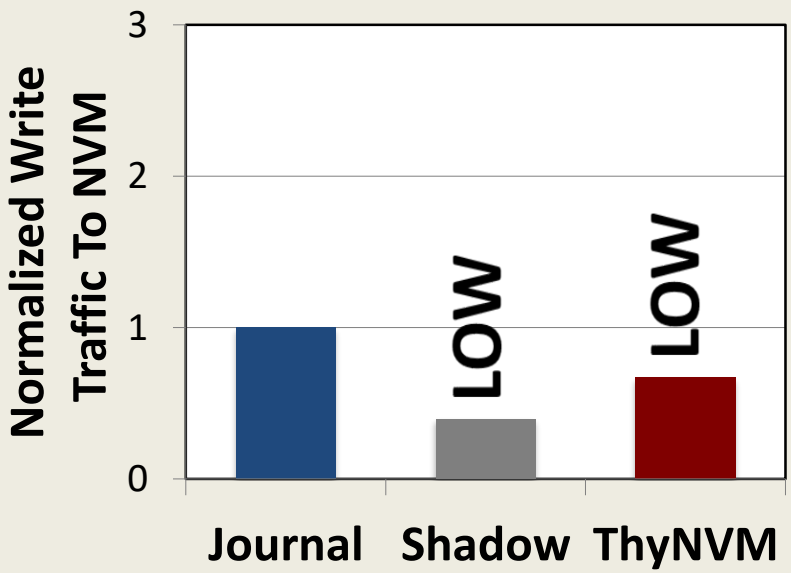
Shadow Paging: Hybrid, copy-on-write pages
- Leverages DRAM to buffer dirty pages

ADAPTIVITY TO ACCESS PATTERN

RANDOM



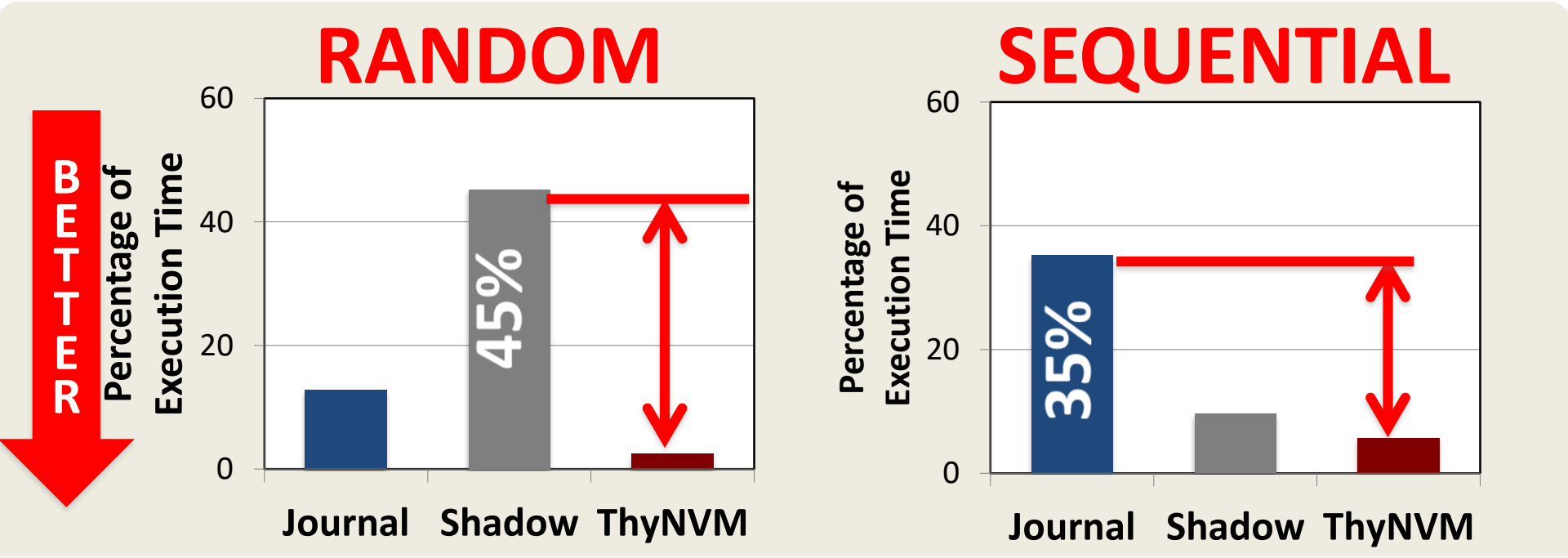
SEQUENTIAL



Journaling is better for Random and Shadow paging is better for Sequential

ThyNVM adapts to both access patterns

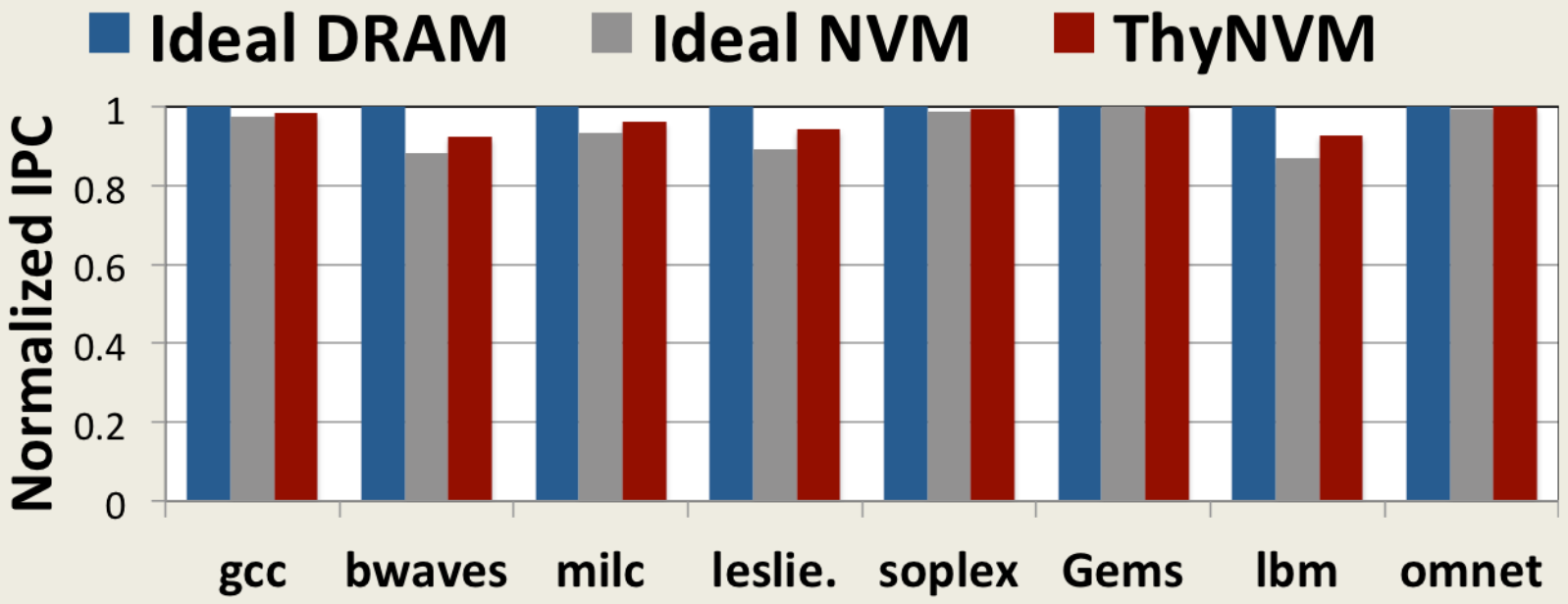
OVERLAPPING CHECKPOINTING AND EXECUTION



Can spend 35-45% of the execution on checkpointing

Stalls the application for a negligible time

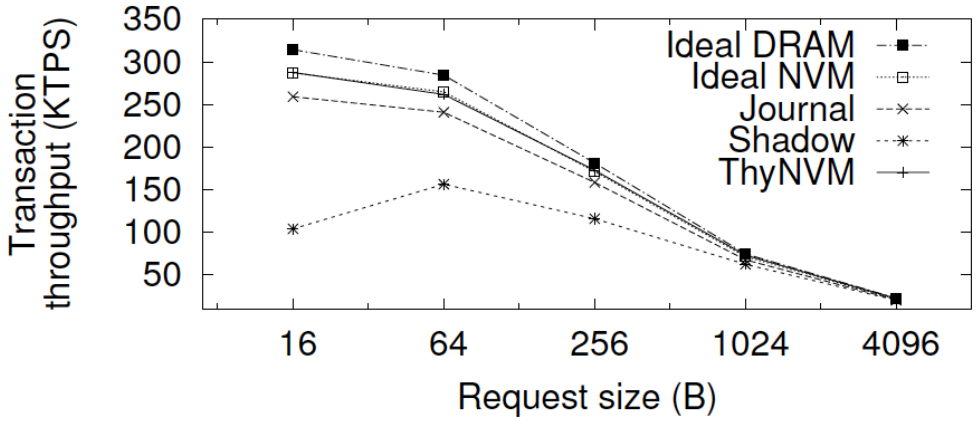
PERFORMANCE OF LEGACY CODE



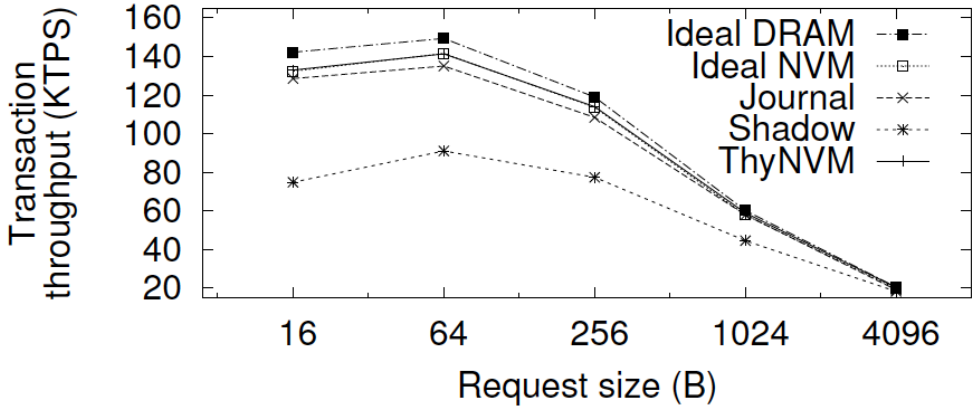
Within -4.9%/+2.7% of an idealized DRAM/NVM system

Provides consistency without significant performance overhead

KEY-VALUE STORE TX THROUGHPUT



(a) Hash table based key-value store



(b) Red-black tree based key-value store

Figure 9: Transaction throughput for two key-value stores: (a) hash table based, (b) red-black tree based.

Storage throughput close to Ideal DRAM

OUTLINE

Crash Consistency Problem

Current Solutions

ThyNVM

Evaluation

Conclusion

ThyNVM

A new **hardware-based** *checkpointing mechanism*, **with no programming effort**

- **Checkpoints** at *multiple granularities* to minimize both latency and metadata
- **Overlaps** *checkpointing* and *execution*
- **Adapts** to *DRAM and NVM* characteristics

Can enable widespread *adoption* of persistent memory

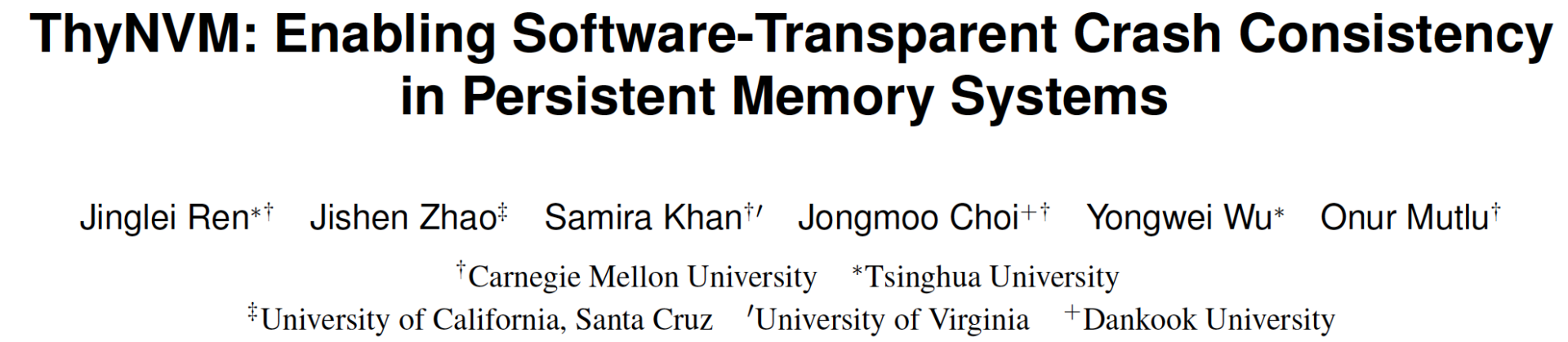
Source Code and More Available at
http://persper.com/thynvm

ThyNVM

Enabling Software-transparent Crash Consistency In Persistent Memory Systems

More About ThyNVM

- Jinglei Ren, Jishen Zhao, Samira Khan, Jongmoo Choi, Yongwei Wu, and Onur Mutlu,
  "ThyNVM: Enabling Software-Transparent Crash Consistency in Persistent Memory Systems"
  *Proceedings of the 48th International Symposium on Microarchitecture (**MICRO**)*, Waikiki, Hawaii, USA, December 2015.
  [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Poster (pptx) (pdf)]
  [Source Code]



ThyNVM: Enabling Software-Transparent Crash Consistency in Persistent Memory Systems

Jinglei Ren[*†] Jishen Zhao[‡] Samira Khan[†′] Jongmoo Choi[+†] Yongwei Wu[*] Onur Mutlu[†]

[†]Carnegie Mellon University [*]Tsinghua University
[‡]University of California, Santa Cruz [′]University of Virginia [+]Dankook University

Another Key Challenge in Persistent Memory

Programming Ease

to Exploit Persistence

Tools/Libraries to Help Programmers

- Himanshu Chauhan, Irina Calciu, Vijay Chidambaram, Eric Schkufza, Onur Mutlu, and Pratap Subrahmanyam, **"NVMove: Helping Programmers Move to Byte-Based Persistence"**
  *Proceedings of the 4th Workshop on Interactions of NVM/Flash with Operating Systems and Workloads (**INFLOW**)*, Savannah, GA, USA, November 2016.
  [Slides (pptx) (pdf)]

NVMove: Helping Programmers Move to Byte-Based Persistence

Himanshu Chauhan *
UT Austin

Irina Calciu
VMware Research Group

Vijay Chidambaram
UT Austin

Eric Schkufza
VMware Research Group

Onur Mutlu
ETH Zürich

Pratap Subrahmanyam
VMware

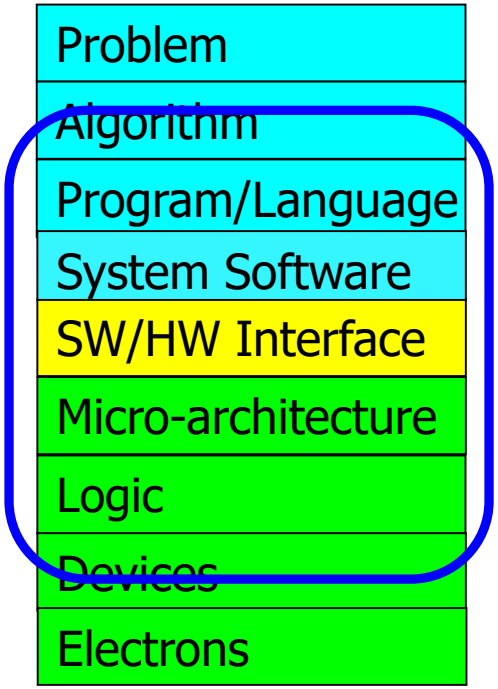
The Future of Emerging Technologies is Bright

- Regardless of challenges
  - in underlying technology and overlying problems/requirements

Can enable:

- Orders of magnitude improvements

- New applications and computing systems



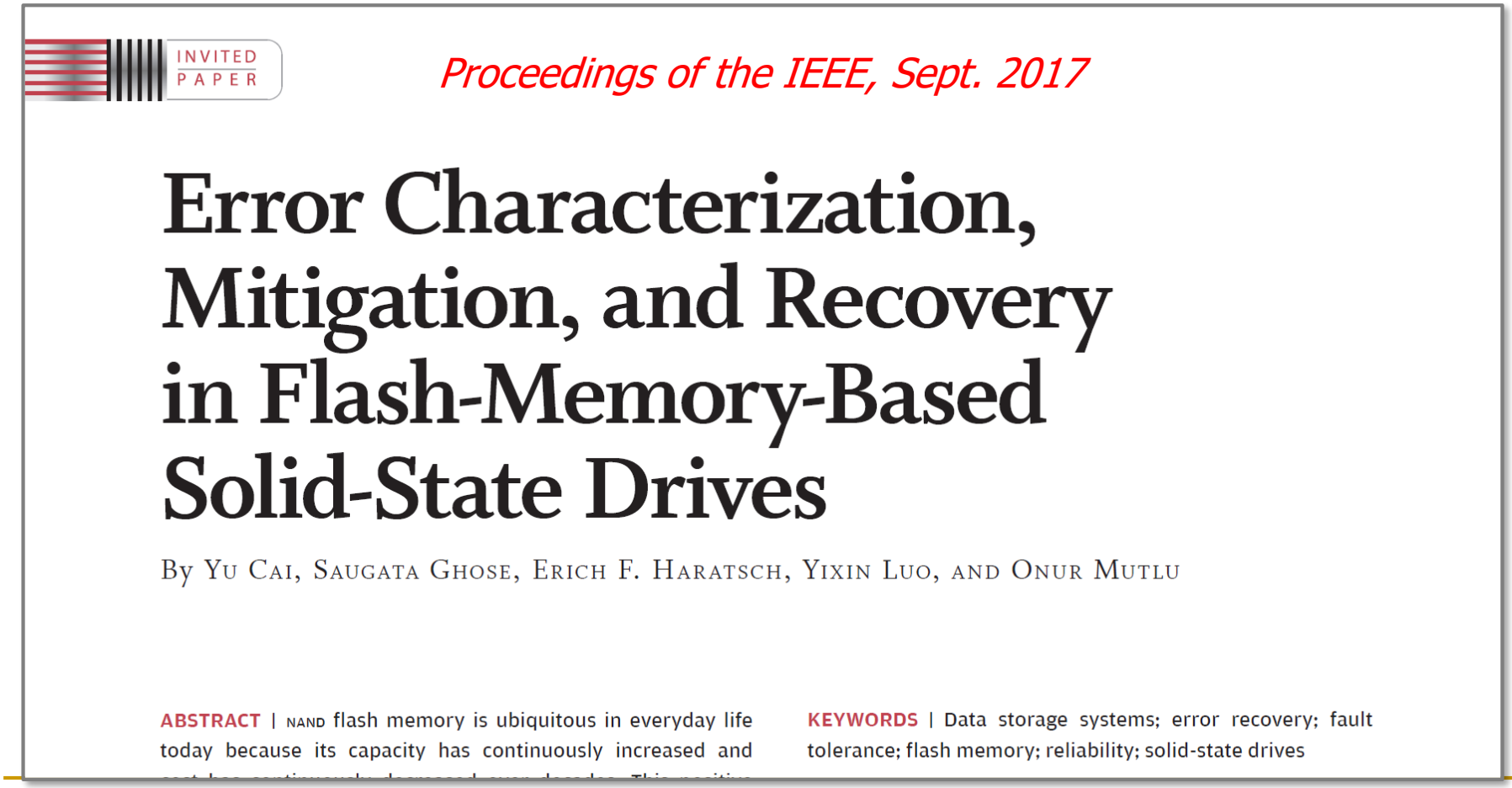
Yet, we have to

- Think across the stack

- Design enabling systems

If In Doubt, Refer to Flash Memory

- A very "doubtful" emerging technology
  - for at least two decades



https://arxiv.org/pdf/1706.08642